Dialog DataStar

options | logoff | feedback | help

United States Patent and Trademark Office

sira

database | easy search

Advanced Search:

Inspec - 1969 to date (INZZ)

limit

Search history:

No.	Database	Search term	Info added since	Results	
1	INZZ	magnetoresistive OR magnetoresistance OR MR OR GMR	unrestricted	45714	show titles
2	INZZ	gate ADJ electrode	unrestricted	2068	show titles
3	INZZ	1 AND 2	unrestricted	22	show titles
4	INZZ	active ADJ region	unrestricted	7618	show titles
5	INZZ	1 AND 4	unrestricted	20	show titles
6	INZZ	2 AND 4	unrestricted	5	show titles
7	INZZ	5 AND 6	unrestricted	0	-
8	INZZ	sensitive ADJ region	unrestricted	256	show titles
9	INZZ	1 AND 8	unrestricted	4	show titles
10	INZZ	2 AND 8	unrestricted	0	-

hide | delete all search steps... | delete individual search steps...

Enter your search term(s): Search tips ☐ Thesaurus mapping

valence and conductive and carrier adj density | whole document

Information added since: [ ] or: [none] search
(YYYYMMDD)

Select special search terms from the following list(s):

- Publication year
- Inspec thesaurus - browse headings A-G
- Inspec thesaurus - browse headings H-Q
- Inspec thesaurus - browse headings R-Z
- Inspec thesaurus - enter a term
- Classification codes A: Physics, 0-1
- Classification codes A: Physics, 2-3
- Classification codes A: Physics, 4-5
- Classification codes A: Physics, 6
- Classification codes A: Physics, 7
- Classification codes A: Physics, 8
- Classification codes A: Physics, 9
- Classification codes B: Electrical & Electronics, 0-5
- Classification codes B: Electrical & Electronics, 6-9
- Classification codes C: Computer & Control
- Classification codes D: Information Technology
- Classification codes E: Mech., Manufac. & Production Engineering
- Treatment codes
- Inspec sub-file
- Language of publication
- Publication types

Top - News & FAQS - Dialog

Dialog DataStar

options | logoff | feedback | help

databases | easy search

Advanced Search:

Inspec - 1969 to date (INZZ)

limit

Search history:

No.	Database	Search term	Info added since	Results	
8	INZZ	sensitive ADJ region	unrestricted	256	show titles
9	INZZ	1 AND 8	unrestricted	4	show titles
10	INZZ	2 AND 8	unrestricted	0	-
11	INZZ	valence AND conductive AND carrier ADJ density	unrestricted	3	show titles
12	INZZ	valence AND conduction AND carrier ADJ density	unrestricted	377	show titles
13	INZZ	1 AND 12	unrestricted	35	show titles
14	INZZ	1 AND 12	unrestricted	35	show titles
15	INZZ	ferromagnetic AND paramagnetic	unrestricted	8830	show titles
16	INZZ	1 AND 15	unrestricted	934	show titles
17	INZZ	2 AND 16	unrestricted	0	-

show all | hide | delete all search steps... | delete individual search steps...

Enter your search term(s): Search tips ☐ Thesaurus mapping

whole document

Information added since: or: none search
(YYYYMMDD)

Select special search terms from the following list(s):

- Publication year
- Inspec thesaurus - browse headings A-G
- Inspec thesaurus - browse headings H-Q
- Inspec thesaurus - browse headings R-Z
- Inspec thesaurus - enter a term
- Classification codes A: Physics, 0-1
- Classification codes A: Physics, 2-3
- Classification codes A: Physics, 4-5
- Classification codes A: Physics, 6
- Classification codes A: Physics, 7
- Classification codes A: Physics, 8
- Classification codes A: Physics, 9
- Classification codes B: Electrical & Electronics, 0-5
- Classification codes B: Electrical & Electronics, 6-9
- Classification codes C: Computer & Control
- Classification codes D: Information Technology
- Classification codes E: Mech., Manufac. & Production Engineering
- Treatment codes
- Inspec sub-file
- Language of publication
- Publication types

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	"5416353".pn.	US-PGPUB; USPAT	OR	OFF	2006/02/20 22:41
L2	303118	(control$5).clm.	US-PGPUB	OR	ON	2006/02/20 22:42
L3	114949	(chang$5).clm.	US-PGPUB	OR	ON	2006/02/20 22:42
L4	102653	(adjust$5).clm.	US-PGPUB	OR	ON	2006/02/20 22:42
L5	40	(stripe adj height).clm.	US-PGPUB	OR	ON	2006/02/20 22:42
L6	167752	(active region).clm.	US-PGPUB	OR	ON	2006/02/20 22:42
L7	3508	(active adj region).clm.	US-PGPUB	OR	ON	2006/02/20 22:42
L8	115	(sensitive adj region).clm.	US-PGPUB	OR	ON	2006/02/20 22:44
L9	176931	(size width height depth narrowed widened).clm.	US-PGPUB	OR	ON	2006/02/20 22:43
L10	117338	(2 3 4) and (5 6 7 8 9)	US-PGPUB	OR	ON	2006/02/20 22:43
L11	14671	(2 3 4) and (9) and (5 6 7 8)	US-PGPUB	OR	ON	2006/02/20 22:44
L12	405	(2 3 4) and (9) and (5 7 8)	US-PGPUB	OR	ON	2006/02/20 22:44
L13	3224	(MR magnetoresist$5 GMR SVMR TMR TJMR).clm.	US-PGPUB	OR	ON	2006/02/20 22:44
L14	13	12 and 13	US-PGPUB	OR	ON	2006/02/20 22:44

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	12	(US-20040061980-$ or US-20040218499-$ or US-20050117263-$ or US-20050230676-$ or US-20040183132-$).did. or (US-6952328-$ or US-6697235-$ or US-6693299-$ or US-5650338-$).did. or (JP-2004128085-$).did. or (JP-2000031298-$ or US-20050184285-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2006/02/20 22:15
S1	282	(360/313).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/19 18:19
S2	617	(360/324.12).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:07
S3	209	(360/324).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/19 18:19
S4	132	(360/320).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/19 18:19
S5	1186	S2 S1 S3 S4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/19 18:25
S6	41	S5 and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/19 18:25
S7	7510148	control$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:07

EAST Search History

S8	4272927	chang$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:07
S9	7465860	size volume area width length depth	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:08
S10	1429174	(S7 S8) with S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:08
S11	1074076	narrow$4 widen$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:09
S12	2241413	active sensitive	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:09
S13	6539899	region zone area element	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:09
S14	2260754	S10 S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:09
S15	201413	S12 near3 S13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:10
S16	10002	S14 with S15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:10
S17	2596161	voltage potential	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:10

EAST Search History

S18	1175	S16 same S17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:10
S19	82685	MR magnetoresist$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:11
S20	7	S18 same S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:12
S21	161515	gate adj3 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:12
S22	89	S18 same S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:30
S23	183180	("360"/$ "369"/$ "720"/$ 29/603$).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:30
S24	1603309	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:30
S25	1445372	magnetic (magnetism near2 sensitive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:30
S26	6980	S23 and S24 and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:30
S27	3236	S23 and S24 same S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:39

EAST Search History

S28	1779	chalcopyrite	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:39
S29	1	S27 and S28	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:39
S30	6	S26 and S28	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:42
S31	159378	gate adj2 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:43
S32	9540	S31 with "26"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:43
S33	24835	S31 same S12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:43
S34	15328	S31 same (S12 with S13)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:45
S35	2508	S17 same S34	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 12:45
S36	810	(S7 S8) same S35	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 18:20
S37	824	valence and (conduction conductive) and (carrier near2 density)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 18:21

EAST Search History

S38	541	"23" and S37	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 18:21
S39	183180	("360"/$ "369"/$ "720"/$ 29/603$).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 18:21
S40	7	S39 and S37	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 18:39
S41	26	("6373667" "6230389" "6496333" "6449131" "6430015" "6310751" "6230690" "5783460" "5684568" "5653013" "5546254" "5079831" "6204071").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/20 18:40
S42	13	("6373667" "6230389" "6496333" "6449131" "6430015" "6310751" "6230690" "5783460" "5684568" "5653013" "5546254" "5079831" "6204071").pn.	USPAT	OR	OFF	2006/02/20 18:47
S43	3	("5251088" "6934133").pn. ("20020135948").did.	US-PGPUB; USPAT	OR	OFF	2006/02/20 18:48

```
File   2:INSPEC 1898-2006/Feb W2
         (c) 2006 Institution of Electrical Engineers
File   6:NTIS 1964-2006/Feb W1
         (c) 2006 NTIS, Intl Cpyrght All Rights Res
File   8:Ei Compendex(R) 1970-2006/Feb W2
         (c) 2006 Elsevier Eng.  Info. Inc.
File  34:SciSearch(R) Cited Ref Sci 1990-2006/Feb W3
         (c) 2006 Inst for Sci Info
File  35:Dissertation Abs Online 1861-2006/Jan
         (c) 2006 ProQuest Info&Learning
File  56:Computer and Information Systems Abstracts 1966-2006/Feb
         (c) 2006 CSA.
File  57:Electronics & Communications Abstracts 1966-2006/Feb
         (c) 2006 CSA.
File  65:Inside Conferences 1993-2006/Feb W3
         (c) 2006 BLDSC all rts. reserv.
File  94:JICST-EPlus 1985-2006/Nov W4
         (c)2006 Japan Science and Tech Corp(JST)
File  95:TEME-Technology & Management 1989-2006/Feb W3
         (c) 2006 FIZ TECHNIK
File  99:Wilson Appl. Sci & Tech Abs 1983-2006/Jan
         (c) 2006 The HW Wilson Co.
File 144:Pascal 1973-2006/Jan W5
         (c) 2006 INIST/CNRS
File 256:TecInfoSource 82-2006/Feb
         (c) 2006 Info.Sources Inc
File 434:SciSearch(R) Cited Ref Sci 1974-1989/Dec
         (c) 1998 Inst for Sci Info
File 583:Gale Group Globalbase(TM) 1986-2002/Dec 13
         (c) 2002 The Gale Group
File 603:Newspaper Abstracts 1984-1988
         (c)2001 ProQuest Info&Learning
File 483:Newspaper Abs Daily 1986-2006/Feb 22
         (c) 2006 ProQuest Info&Learning
File 248:PIRA 1975-2006/Jan W5
         (c) 2006 Pira International

Set     Items   Description
S1     111553   (MAGNET? OR MR OR GMR OR GIANT()MAGNETORESISTANCE)(3N)(HEA-
             D?? OR ELEMENT?? OR SENSOR?? OR SENSING OR SENSITIVE OR ACTIVE
              OR TRANSDUCER??)
S2       2594   STRIPE??()(WIDTH?? OR HEIGHT OR AREA?? OR SIZE?? OR VOLUME-
             ?? OR DEPTH OR PORTION?? OR REGION?? OR ZONE??)
S3        259   (CONTROL? OR CHANGE?? OR CHANGING OR WIDEN??? OR NARROW???
             OR MODIFY??? OR MODIFY? OR REDUCE?? OR REDUCING OR SHRINK???)-
             (3N)S2
S4     375878   STACK??? OR (PLURAL? OR MANY OR MULTIPLE?? OR MANY OR SEVE-
             RAL OR MULTI OR NUMEROUS OR SUBSTRATE)(3N)LAYER??
S5      33997   AU=(HANEDA, S? OR HANEDA S? OR OSAWA, Y? OR OSAWA Y? OR NA-
             KAMURA, S? OR NAKAMURA S?)
S6        390   (GATE()ELECTRODE??)(3N)VOLT????
S7          0   S1(3N)S3
S8         15   S1(3N)S2
S9          0   S8(3N)S4
S10         0   S8 AND S4
S11         4   RD S8  (unique items)
S12         0   S3(3N)S6
S13         2   S2(3N)S4
S14         2   S13 NOT S11
S15       130   S1(3N)S4
S16         0   S15(3N)S6
```

S17	0	S15 AND S6
S18	1	S15 AND S2
S19	1	S18 NOT (S11 OR S14)
S20	0	S3(3N)S4
S21	9	S3 AND S4
S22	5	RD (unique items)
S23	3	S22 NOT (S11 OR S14 OR S19)
S24	0	S3 AND S5
S25	1	S2 AND S5
S26	1	S25 NOT (S11 OR S14 OR S19 OR S23)
S27	1	S15 AND S5
S28	1	S27 NOT (S11 OR S14 OR S19 OR S23 OR S26)
S29	329	S4 AND S5
S30	0	S29(3N)S6
S31	0	S29(3N)S2

11/3,K/1 (Item 1 from file: 2)
DIALOG(R)File 2:INSPEC

08709273 INSPEC Abstract Number: B2003-09-3120J-014
Title: Directional sensitivity of GMR element and its industrial applications
Author(s): Wakiwaka, H.; Kataoka, Y.; Shinoura, O.
Author Affiliation: Fac. of Eng., Shinshu Univ., Nagano, Japan
Journal: International Journal of Applied Electromagnetics and Mechanics Conference Title: Int. J. Appl. Electromagn. Mech. (Netherlands) vol.15, no.1-4 p.89-96
Publisher: IOS Press,
Publication Date: 2001-2002 Country of Publication: Netherlands
CODEN: IJAMFO ISSN: 1383-5416
SICI: 1383-5416(2001/2002)15:1/4L.89:DSEI;1-X
Material Identity Number: E313-2003-003
U.S. Copyright Clearance Center Code: 1383-5416/02/$8.00
Conference Title: Tenth International Symposium on Applied Electromagnetics and Mechanics. ISEM-Tokyo
Conference Date: 13-16 May 2001 Conference Location: Tokyo, Japan
Language: English
Subfile: B

...Abstract: elements are generally used to detect the magnetic field impressed in the direction of the **stripe width** . However, the **GMR element** has high sensitivity in the direction of the length as well as the width, even...

11/3,K/2 (Item 2 from file: 2)
DIALOG(R)File 2:INSPEC

06408753 INSPEC Abstract Number: B9612-3120B-063
Title: Submicron trackwidth and stripe height MR sensor **test structures**
Author(s): Fontana, R.E., Jr.; MacDonald, S.A.; Ching Tsang; Tsann Lin
Author Affiliation: IBM Res. Div., Almaden Res. Center, San Jose, CA, USA
Journal: IEEE Transactions on Magnetics Conference Title: IEEE Trans. Magn. (USA) vol.32, no.5, pt.1 p.3440-2
Publisher: IEEE,
Publication Date: Sept. 1996 Country of Publication: USA
CODEN: IEMGAQ ISSN: 0018-9464
SICI: 0018-9464(199609)32:5:1L.3440:STSH;1-3
Material Identity Number: I101-96007
U.S. Copyright Clearance Center Code: 0018-9464/96/$05.00
Conference Title: 1996 IEEE International Magnetics Conference (INTERMAG '96)
Conference Sponsor: Magn. Soc. IEEE
Conference Date: 9-12 April 1996 Conference Location: Seattle, WA, USA
Language: English
Subfile: B

Title: Submicron trackwidth and stripe height MR sensor **test structures**

11/3,K/3 (Item 3 from file: 2)
DIALOG(R)File 2:INSPEC

05123406 INSPEC Abstract Number: B9205-3120B-042
Title: Micromagnetic track profile asymmetries in dual magnetoresistive heads
Author(s): Nix, L.; Helms, C.; O'Connor, D.
Author Affiliation: Storage Technol. Corp., Louisville, CO, USA
Journal: IEEE Transactions on Magnetics vol.27, no.6, pt.2 p.4693-7
Publication Date: Nov. 1991 Country of Publication: USA
CODEN: IEMGAQ ISSN: 0018-9464
U.S. Copyright Clearance Center Code: 0018-9464/91/$01.00
Conference Title: Fifth Joint Magnetism and Magnetic Materials-Intermag Conference
Conference Sponsor: AIP; IEEE
Conference Date: 18-21 June 1991 Conference Location: Pittsburgh, PA, USA
Language: English
Subfile: B

Abstract: An appropriate 3-D micromagnetic model of a shielded, finite **stripe height**, dual **element magnetoresistive** (**MR**) **head** is developed. It is shown that asymmetric bias profiles in the cross track direction arise...

11/3,K/4 (Item 1 from file: 8)
DIALOG(R)File 8:Ei Compendex(R)

05944602 E.I. No: EIP01476741006
Title: Effect of current density and stripe height on the amplitude of a dual-synthetic GMR head
Author: Li, Y.
Corporate Source: Read-Rite Corporation, Milpitas, CA 95035, United States
Conference Title: 8th Joint Magnetism and Magnetic Materials -International Magnetic Conference- (MMM-Intermag)
Conference Location: San Antonio, TX, United States Conference Date: 20010107-20010111
E.I. Conference No.: 58692
Source: IEEE Transactions on Magnetics v 37 n 4 I July 2001. p 1695-1697
Publication Year: 2001
CODEN: IEMGAQ ISSN: 0018-9464
Language: English

Identifiers: **Stripe height** ; Dual-synthetic **magnetic heads**

14/3,K/1 (Item 1 from file: 2)
DIALOG(R)File 2:INSPEC

06295238 INSPEC Abstract Number: A9614-4255P-050, B9607-4320J-183
Title: An optimum design of buried heterostructure lasers with minimum threshold current using MEDICI
Author(s): Hyeong Rae Kim; Kae Dal Kwack
Author Affiliation: Dept. of Electr. Eng., Hanyang Univ., Seoul, South Korea
Journal: Journal of the Korean Institute of Telematics and Electronics vol.33A, no.1 p.59-67
Publisher: Korea Inst. Telematics & Electron,
Publication Date: Jan. 1996 Country of Publication: South Korea
CODEN: CKNOEZ ISSN: 1016-135X
SICI: 1016-135X(199601)33A:1L.59:ODBH;1-K
Material Identity Number: N523-96010
Language: Korean
Subfile: A B

...Abstract: InP current blocking layer are fixed to have minimum current leakage, then various simulations with **several** active **layer** thicknesses and **stripe widths** are performed. The stripe width with minimum threshold current varies with the active layer thickness...

14/3,K/2 (Item 2 from file: 2)
DIALOG(R)File 2:INSPEC

04503029 INSPEC Abstract Number: A89133692, B89076702
Title: Development and characterization of a planar double heterostructure laser diode and a stripe double heterostructure grown by MBE
Author(s): Chi Yhou Hong; Tae Won Kang; Youn Hwan Lee; Gi Seok Eom; Deuk Young Kim; Kwan Soo Chung
Author Affiliation: Dept. of Phys., Dongguk Univ., Seoul, South Korea
Journal: New Physics (Korean Physical Society) vol.29, no.3 p. 299-304
Publication Date: June 1989 Country of Publication: South Korea
CODEN: NWPYA4 ISSN: 0374-4914
Language: Korean
Subfile: A B

...Abstract: by molecular beam epitaxy, and their properties have been investigated as a function of the **substrate** temperature, the active **layer** thickness and the **stripe width** . The optical quality of Al/sub x/Ga/sub 1-x/As layer was observed...

19/3,K/1 (Item 1 from file: 2)
DIALOG(R)File 2:INSPEC

08479682 INSPEC Abstract Number: B2003-01-3120J-036, C2003-01-5320C-086
Title: Thermally activated magnetic noise and spectra in GMR heads
Author(s): Jian-Gang Zhu; Yuchen Zhou
Author Affiliation: Dept. of Electr. Eng., Carnegie Mellon Univ., Pittsburgh, PA, USA
Conference Title: Intermag Europe 2002 Digest of Technical Papers. 2002 IEEE International Magnetics Conference (Cat.No.02CH37323) p.BP9
Publisher: IEEE, Piscataway, NJ, USA
Publication Date: 2002 Country of Publication: USA vii+513 pp.
ISBN: 0 7803 7365 0 Material Identity Number: XX-2002-01368
U.S. Copyright Clearance Center Code: 0-7803-7365-0/02/$17.00
Conference Title: Intermag Europe 2002 Digest of Technical Papers. 2002 IEEE International Magnetics Conference
Conference Sponsor: Magnetic Soc. IEEE
Conference Date: 28 April-2 May 2002 Conference Location: Amsterdam, Netherlands
Language: English
Subfile: B C

...Abstract: spin valve GMR heads. It is found that at W=200 nm and a nominal **stripe height** , the noise spectra exhibits multiple resonance frequencies, indicating a spatial non-uniformity of the magnetization precessions over the free layer. At a slightly narrower track width and a reduced **stripe height** , the multimode feature reduces to a virtually single mode resonance. Micromagnetic simulation shows that increasing sensor **stripe height** significantly yields a significant increase of mag-noise level in the low frequency region. Detailed...

... presented in the paper on the multimode excitation conditions. Analysis on the head designs with **multiple** sense **layers** such as CPP/ **GMR head** is also presented.
...Identifiers: sensor **stripe height** ;

23/3,K/1 (Item 1 from file: 2)
DIALOG(R)File 2:INSPEC

05893981 INSPEC Abstract Number: A9507-4260B-017, B9504-4320J-057
Title: Monolithically integrated multi-wavelength MQW-DBR laser diodes fabricated by selective metalorganic vapor phase epitaxy
Author(s): Sasaki, T.; Yamaguchi, M.; Kitamura, M.
Author Affiliation: Opto-Electron. Res. Labs., NEC Corp., Ibaraki, Japan
Journal: Journal of Crystal Growth vol.145, no.1-4 p.846-51
Publication Date: Dec. 1994 Country of Publication: Netherlands
CODEN: JCRGAE ISSN: 0022-0248
U.S. Copyright Clearance Center Code: 0022-0248/94/$07.00
Conference Title: Seventh International Conference on Metalorganic Vapor Phase Epitaxy
Conference Date: 31 May-3 June 1994 Conference Location: Yokohama, Japan
Language: English
Subfile: A B

Abstract: Selective metalorganic vapor phase epitaxy (MOVPE) was used to grow InGaAsP/InP **layers** for fabricating **multi** -wavelength laser diodes. Multiple quantum well (MQW) active and passive waveguides were simultaneously grown by...
... the effective refractive index of the MQW passive waveguide at the DBR region can be **controlled** by the mask **stripe width** . This simple technique was used to fabricate multi-wavelength MQW-DBR laser diodes. In the...

23/3,K/2 (Item 1 from file: 94)
DIALOG(R)File 94:JICST-EPlus

04929320 JICST ACCESSION NUMBER: 01A0803563 FILE SEGMENT: JICST-E
AlGaInN-based high power lasers.
TAKEYA MOTONOBU (1); TOJO TSUYOSHI (1); ASANO TAKEHARU (1); HINO TOMONORI (1); KIJIMA SATORU (1); GOTO OSAMU (1); UCHIDA SHIRO (1); IKEDA MASAO (1)
(1) Sonishiraishisemikondakuta Kaise
Denshi Joho Tsushin Gakkai Gijutsu Kenkyu Hokoku(IEIC Technical Report (Institute of Electronics, Information and Communication Enginners), 2001, VOL.101,NO.113(LQE2001 16-30), PAGE.79-84, FIG.8, REF.11
JOURNAL NUMBER: S0532BBG
UNIVERSAL DECIMAL CLASSIFICATION: 621.375.826:621.315.592
LANGUAGE: Japanese COUNTRY OF PUBLICATION: Japan
DOCUMENT TYPE: Journal
ARTICLE TYPE: Original paper
MEDIA TYPE: Printed Publication

...ABSTRACT: new laser structure that could suppress the generation of first-order transverse mode and by **narrowing** the ridge **stripe width** . Besides, the threshold current and slope efficiency were improved by introducing a GaInN inter- **layer** between a **multiple** -quantum well active **layer** and an AlGaN layer. The threshold current density was -3.5kA/cm2 and the slope...

23/3,K/3 (Item 1 from file: 95)

00755343 I93116094320

Selective metalorganic vapor phase epitaxial growth of InGaAsP/InP layers with bandgap energy control in InGaAs/InGaAsP multiple-quantum well structures

(Selektives metallorganisches Gasphasenepitaxialwachstum von InGaAsP/InP mit Bandlueckenenergieregelung in InGaAs/InGaAsP-Mehrfach-Quantentopfstrukturen)

Sasaki, T; Kitamura, M; Mito, I
Opto-Electron. Res. Labs., NEC Corp., Ibaraki, Japan

Journal of Crystal Growth, v132, n3-4, pp435-443, 1993
Document type: journal article Language: English
Record type: Abstract
ISSN: 0022-0248

ABSTRACT:
...MQW) ridge structures with crystallographically smooth side facets and flat interfaces are successfully obtained. By **changing** the mask **stripe width** the bandgap energy of the MQW structure is modified.
...IDENTIFIERS: SELECTIVE METALORGANIC VAPOR PHASE EPITAXIAL GROWTH; BANDGAP ENERGY CONTROL; PASSIVE WAVEGUIDE LAYERS; PHOTONIC DEVICES; OPEN **STRIPE REGIONS** ; **NARROW** GROWTH REGIONS; LAYER THICKNESSES; TOP SURFACE; FLAT GROWN SURFACE; SURFACE MIGRATED SPECIES; MIGRATION LENGTHS; CRYSTALLOGRAPHICALLY SMOOTH SIDE FACETS; FLAT INTERFACES; MASK STRIPE WIDTH ; MASK PATTERNED PLANAR INP **SUBSTRATE** ; INGAASP INP **LAYERS** ; Gasphasenepitaxie; Energieband

26/3,K/1 (Item 1 from file: 2)
DIALOG(R)File 2:INSPEC

01405308 INSPEC Abstract Number: A72042093, B72023988
Title: Very-low-current operation of mesa-stripe-geometry double-heterostructure injection lasers
Author(s): Tsukada, T.; Nakashima, H.; Umeda, J.; **Nakamura, S.** ; Chinone, N.; Ito, R.; Nakada, O.
Author Affiliation: Hitachi, Ltd., Kokubunji, Tokyo, Japan
Journal: Applied Physics Letters vol.20, no.9 p.344-5
Publication Date: 1 May 1972 Country of Publication: USA
CODEN: APPLAB ISSN: 0003-6951
Language: English
Subfile: A B

Author(s): Tsukada, T.; Nakashima, H.; Umeda, J.; **Nakamura, S.** ; Chinone, N.; Ito, R.; Nakada, O.
...Abstract: been fabricated. Lasers of this geometry are made by etching the heterostructure layers, leaving a **stripe region** with a width ranging from 10 to 40 mu m. The current-spreading effect inherent...

28/3,K/1 (Item 1 from file: 144)
DIALOG(R)File 144:Pascal

10116521 PASCAL No.: 92-0322142
Stacked optical disk drive for multimedia files
Optical memories
NAKAMURA S ; SEYA E; SUKEDA H; MATSUMOTO K; NIIHARA T; NIHEI H; ICHIKAWA K; MITA S
Hitachi Ltd, central res. lab., Kokubunjl Tokyo 185, Japan
Journal: Japanese journal of applied physics, 1992, 31 (2B p.1) 625-629
Language: English

NAKAMURA S ; SEYA E; SUKEDA H; MATSUMOTO K; NIIHARA T; NIHEI H; ICHIKAWA K; MITA S

English Descriptors: Optical disk; Optical recording; Multimedia; **Stacking** ; Drive mechanism; Optical **head** ; **Magnetooptical** disk

File 9:Business & Industry(R) Jul/1994-2006/Feb 23
(c) 2006 The Gale Group
File 15:ABI/Inform(R) 1971-2006/Feb 24
(c) 2006 ProQuest Info&Learning
File 16:Gale Group PROMT(R) 1990-2006/Feb 24
(c) 2006 The Gale Group
File 20:Dialog Global Reporter 1997-2006/Feb 24
(c) 2006 Dialog
File 47:Gale Group Magazine DB(TM) 1959-2006/Feb 23
(c) 2006 The Gale group
File 75:TGG Management Contents(R) 86-2006/Feb W2
(c) 2006 The Gale Group
File 80:TGG Aerospace/Def.Mkts(R) 1982-2006/Feb 23
(c) 2006 The Gale Group
File 88:Gale Group Business A.R.T.S. 1976-2006/Feb 17
(c) 2006 The Gale Group
File 98:General Sci Abs 1984-2004/Dec
(c) 2005 The HW Wilson Co.
File 112:UBM Industry News 1998-2004/Jan 27
(c) 2004 United Business Media
File 141:Readers Guide 1983-2004/Dec
(c) 2005 The HW Wilson Co
File 148:Gale Group Trade & Industry DB 1976-2006/Feb 23
(c)2006 The Gale Group
File 160:Gale Group PROMT(R) 1972-1989
(c) 1999 The Gale Group
File 275:Gale Group Computer DB(TM) 1983-2006/Feb 23
(c) 2006 The Gale Group
File 264:DIALOG Defense Newsletters 1989-2006/Feb 22
(c) 2006 Dialog
File 484:Periodical Abs Plustext 1986-2006/Feb W3
(c) 2006 ProQuest
File 553:Wilson Bus. Abs. 1982-2004/Dec
(c) 2005 The HW Wilson Co
File 570:Gale Group MARS(R) 1984-2006/Feb 23
(c) 2006 The Gale Group
File 608:KR/T Bus.News. 1992-2006/Feb 24
(c)2006 Knight Ridder/Tribune Bus News
File 620:EIU:Viewswire 2005/Oct 19
(c) 2005 Economist Intelligence Unit
File 613:PR Newswire 1999-2006/Feb 24
(c) 2006 PR Newswire Association Inc
File 621:Gale Group New Prod.Annou.(R) 1985-2006/Feb 23
(c) 2006 The Gale Group
File 623:Business Week 1985-2006/Feb 24
(c) 2006 The McGraw-Hill Companies Inc
File 624:McGraw-Hill Publications 1985-2006/Feb 24
(c) 2006 McGraw-Hill Co. Inc
File 634:San Jose Mercury Jun 1985-2006/Feb 23
(c) 2006 San Jose Mercury News
File 635:Business Dateline(R) 1985-2006/Feb 24
(c) 2006 ProQuest Info&Learning
File 636:Gale Group Newsletter DB(TM) 1987-2006/Feb 23
(c) 2006 The Gale Group
File 647:CMP Computer Fulltext 1988-2006/Mar W1
(c) 2006 CMP Media, LLC
File 696:DIALOG Telecom. Newsletters 1995-2006/Feb 23
(c) 2006 Dialog
File 674:Computer News Fulltext 1989-2005/Oct W2
(c) 2005 IDG Communications
File 810:Business Wire 1986-1999/Feb 28

(c) 1999 Business Wire
File 813:PR Newswire 1987-1999/Apr 30
(c) 1999 PR Newswire Association Inc
File 587:Jane`s Defense&Aerospace 2006/Feb W3
(c) 2006 Jane`s Information Group

Set	Items	Description
S1	159929	(MAGNET? OR MR OR GMR OR GIANT()MAGNETORESISTANCE)(3N)(HEAD?? OR ELEMENT?? OR SENSOR?? OR SENSING OR SENSITIVE OR ACTIVE OR TRANSDUCER??)
S2	654	STRIPE??()(WIDTH?? OR HEIGHT OR AREA?? OR SIZE?? OR VOLUME?? OR DEPTH OR PORTION?? OR REGION?? OR ZONE??)
S3	56	(CONTROL? OR CHANGE?? OR CHANGING OR WIDEN??? OR NARROW??? OR MODIFY??? OR MODIFY? OR REDUCE?? OR REDUCING OR SHRINK???)(3N)S2
S4	675671	STACK??? OR (PLURAL? OR MANY OR MULTIPLE?? OR MANY OR SEVERAL OR MULTI OR NUMEROUS OR SUBSTRATE)(3N)LAYER??
S5	384	AU=(HANEDA, S? OR HANEDA S? OR OSAWA, Y? OR OSAWA Y? OR NAKAMURA, S? OR NAKAMURA S?)
S6	92	(GATE()ELECTRODE??)(3N)VOLT????
S7	0	S3(3N)S4
S8	0	S3(3N)S6
S9	0	S2(3N)S4
S10	0	S2(3N)S6
S11	0	S2 AND S5
S12	6	S1(3N)S2
S13	3	RD (unique items)
S14	0	S1 AND S5

13/3,K/1 (Item 1 from file: 16)
DIALOG(R)File 16:Gale Group PROMT(R)

06346588 Supplier Number: 54653481 (USE FORMAT 7 FOR FULLTEXT)
Ultratech Introduces New-Generation Stepper Family for Advanced Thin-Film Head Production; XLS 9000-Series Platform Tailored for Advanced TFH Lithography.
Business Wire, p0106
May 18, 1999
Language: English Record Type: Fulltext
Document Type: Newswire; Trade
Word Count: 752

... stage, coupled with low-lens distortion, provides the colinearity needed to control the throat and **stripe height** of **GMR** thin film **heads** .
The reticle library for the XLS 9000-series has been expanded to handle up to...

13/3,K/2 (Item 1 from file: 88)
DIALOG(R)File 88:Gale Group Business A.R.T.S.

05934716 SUPPLIER NUMBER: 78966753
Effect of Current Density and Stripe Height on the Amplitude of a Dual-Synthetic GMR Head.
Li, Yufeng
IEEE Transactions on Magnetics, 37, 4, 1695
July, 2001
ISSN: 0018-9464 LANGUAGE: English RECORD TYPE: Abstract

...AUTHOR ABSTRACT: height reduction as compared with current density enhancement.
Index Terms--Amplitude, current density, dual-synthetic **GMR head** , **stripe height** .

13/3,K/3 (Item 2 from file: 88)
DIALOG(R)File 88:Gale Group Business A.R.T.S.

04222875 SUPPLIER NUMBER: 19264658
Submicron trackwidth and stripe height MR sensor **test structures. (** magnetoresistive **)(The 1996 IEEE International Magnetics Conference)(INTERMAG '96)**
Fontana, Robert E., Jr.; MacDonald, Scott A.; Tsang, Ching; Lin, Tsann
IEEE Transactions on Magnetics, v32, n5, p3440(3)
Sep, 1996
ISSN: 0018-9464 LANGUAGE: English RECORD TYPE: Abstract

Submicron trackwidth and stripe height MR sensor **test structures. (** magnetoresistive **)(The 1996 IEEE International Magnetics Conference)(INTERMAG '96)**

File 344:Chinese Patents Abs Jan 1985-2006/Jan
(c) 2006 European Patent Office
File 347:JAPIO Nov 1976-2005/Oct(Updated 060203)
(c) 2006 JPO & JAPIO
File 350:Derwent WPIX 1963-2006/UD,UM &UP=200612
(c) 2006 Thomson Derwent
File 371:French Patents 1961-2002/BOPI 200209
(c) 2002 INPI. All rts. reserv.

Set	Items	Description
S1	174347	(MAGNET? OR MR OR GMR OR GIANT()MAGNETORESISTANCE)(3N)(HEAD?? OR ELEMENT?? OR SENSOR?? OR SENSING OR SENSITIVE OR ACTIVE OR TRANSDUCER??)
S2	1397	STRIPE??()(WIDTH?? OR HEIGHT OR AREA?? OR SIZE?? OR VOLUME?? OR DEPTH OR PORTION?? OR REGION?? OR ZONE??)
S3	153	(CONTROL? OR CHANGE?? OR CHANGING OR WIDEN??? OR NARROW??? OR MODIFY??? OR MODIFY? OR REDUCE?? OR REDUCING OR SHRINK???)(3N)S2
S4	454107	STACK??? OR (PLURAL? OR MANY OR MULTIPLE?? OR MANY OR SEVERAL OR MULTI OR NUMEROUS OR SUBSTRATE)(3N)LAYER??
S5	23497	AU=(HANEDA, S? OR HANEDA S? OR OSAWA, Y? OR OSAWA Y? OR NAKAMURA, S? OR NAKAMURA S?)
S6	2235	(GATE()ELECTRODE??)(3N)VOLT????
S7	8	S1(3N)S3
S8	0	S7(3N)S4
S9	0	S7(3N)S6
S10	10	(S2 OR S3) AND S5
S11	10	S10 NOT S7
S12	4	S1(S)S2(S)S4
S13	4	S12 NOT (S7 OR S11)

7/3,K/1 (Item 1 from file: 347)
DIALOG(R)File 347:JAPIO

08168268 **Image available**
SENSOR STRIPE ENCAPSULATION LAYER IN READ/WRITE HEAD

PUB. NO.: 2004-281028 [JP 2004281028 A]
PUBLISHED: October 07, 2004 (20041007)
INVENTOR(s): BURBANK DANIEL PAUL
HEIM KEVIN RICHARD
APPLICANT(s): SEAGATE TECHNOLOGY LLC
APPL. NO.: 2003-347014 [JP 2003347014]
FILED: October 06, 2003 (20031006)
PRIORITY: 03 387156 [US 2003387156], US (United States of America), March 12, 2003 (20030312)

ABSTRACT
... are free from chemical and mechanical damages resulting from the wrapping by producing a precisely **controlled stripe height** .

SOLUTION: A **magnetoresistive** read **head** has read head layers that are shaped to form an air bearing surface and a...

7/3,K/2 (Item 2 from file: 347)
DIALOG(R)File 347:JAPIO

05467117 **Image available**
THIN-FILM MAGNETIC HEAD SLIDER

PUB. NO.: 09-081917 [JP 9081917 A]
PUBLISHED: March 28, 1997 (19970328)
INVENTOR(s): KUMAKIRI MICHIO
INOUE ATSUSHI
YOSHITOMI YOSHIHISA
TANIGUCHI YOSHINOBU
APPLICANT(s): SANYO ELECTRIC CO LTD [000188] (A Japanese Company or Corporation), JP (Japan)
APPL. NO.: 07-231576 [JP 95231576]
FILED: September 08, 1995 (19950908)

ABSTRACT
... slider and to improve the yield of products by disposing marker layers for detecting the **change** in the **stripe height** of a **magnetoresistive element** layer by polishing of air bearing surface...

... layers 61, 62, 63 and the third marker layers 71, 72, 73 for detecting the **change** in the **stripe height** of the **MR element** layer 3 by the polishing of the air bearing surface 19. An electrode layer 4...

7/3,K/3 (Item 3 from file: 347)
DIALOG(R)File 347:JAPIO

02076277 **Image available**
MAGNETORESISTANCE EFFECT TYPE SENSOR

PUB. NO.: 61-290377 [JP 61290377 A]

PUBLISHED: December 20, 1986 (19861220)
INVENTOR(s): HAYASHI HISANORI
ABIKO SHUZO
GOTO HIROICHI
KUHARA MASAKAZU
INOUE SHINICHI
SANO HIDETO
APPLICANT(s): CANON ELECTRONICS INC [365668] (A Japanese Company or Corporation), JP (Japan)
APPL. NO.: 60-130792 [JP 85130792]
FILED: June 18, 1985 (19850618)
JOURNAL: Section: P, Section No. 578, Vol. 11, No. 156, Pg. 14, May 21, 1987 (19870521)

ABSTRACT

...CONSTITUTION: **Magnetic** reluctant **elements** constituted of **narrow stripe portions** 3a and 3b of a uniaxially anisotropic permalloy film 3 provided on a substrate 2...

7/3,K/4 (Item 1 from file: 350)
DIALOG(R)File 350:Derwent WPIX
(c) 2006 Thomson Derwent. All rts. reserv.

015832972 **Image available**
WPI Acc No: 2003-895176/200382
XRPX Acc No: N03-714218
Slider bar lapping method in disk drive actuation system, involves actuating shear based transducer in each slider, during lapping on disk, based on sensed stripe height of magnetoresistive element
Patent Assignee: SEAGATE TECHNOLOGY LLC (SEAG-N)
Inventor: ANGELO J E; BOUTAGHOU Z
Number of Countries: 001 Number of Patents: 001
Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week	
US 6568992	B1	20030527	US 2000197226	P	20000414	200382	B
			US 2001828489	A	20010406		

Priority Applications (No Type Date): US 2000197226 P 20000414; US 2001828489 A 20010406
Patent Details:

Patent No	Kind	Lan	Pg	Main IPC	Filing Notes
US 6568992	B1		10	B24B-049/00	Provisional application US 2000197226

Abstract (Basic):
... continues to be lapped until it reaches the desired stripe height. By monitoring the sensed **stripe height** , the transducer is **controlled** to ensure the **MR element** is precisely lapped to the desired stripe height...

7/3,K/5 (Item 2 from file: 350)
DIALOG(R)File 350:Derwent WPIX
(c) 2006 Thomson Derwent. All rts. reserv.

014658440 **Image available**
WPI Acc No: 2002-479144/200251
XRPX Acc No: N02-378405
Magnetoresistive head producing method for disc drive, involves dynamically covering magnetoresistive element to prevent removal of

material from element based on its detected electrical resistance
Patent Assignee: SEAGATE TECHNOLOGY LLC (SEAG-N)
Inventor: HAO S; HOEHN J W; LUSE T A; PETERSON J R; REJDA E F; STOVER L E
Number of Countries: 001 Number of Patents: 001
Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
US 20020057537	A1	20020516	US 2000225348	A	20000815	200251 B
			US 2000241217	A	20001013	
			US 2001930741	A	20010815	

Priority Applications (No Type Date): US 2001930741 A 20010815; US 2000225348 P 20000815; US 2000241217 P 20001013
Patent Details:

Patent No	Kind	Lan	Pg	Main IPC	Filing Notes
US 20020057537	A1		20	G11B-005/33	Provisional application US 2000225348 Provisional application US 2000241217

Abstract (Basic):
... For **controlling stripe height** of **MR element** in **MR head** of disk drive...

7/3,K/6 (Item 3 from file: 350)
DIALOG(R)File 350:Derwent WPIX

014539799 **Image available**
WPI Acc No: 2002-360502/200239
XRPX Acc No: N02-281603
Predictive failure analysis (PFA) method for disk drives, involves comparing measurement of resistance for read sensor, e.g. magnetoresistive head, to baseline and flagging file for corrective action when problem is detected
Patent Assignee: INT BUSINESS MACHINES CORP (IBMC)
Inventor: GILLIS D R; SCHOUTERDEN K V; WOLTER R F
Number of Countries: 001 Number of Patents: 001
Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
US 6359433	B1	20020319	US 99460651	A	19991214	200239 B

Priority Applications (No Type Date): US 99460651 A 19991214
Patent Details:

Patent No	Kind	Lan	Pg	Main IPC	Filing Notes
US 6359433	B1		18	G01R-033/12	

Abstract (Basic):
... 1) A method for qualitatively and quantitatively measuring a **change** in **stripe height** of a **MR head** in a disk drive...

7/3,K/7 (Item 4 from file: 350)
DIALOG(R)File 350:Derwent WPIX

014374349 **Image available**
WPI Acc No: 2002-195052/200225
Related WPI Acc No: 2003-755637
XRPX Acc No: N02-148158
Finishing disc drive slider comprises etching trenches between unfinished sliders, and applying multiple pressures to back surface of one slider

while its front surface contacts lapping surface
Patent Assignee: SEAGATE TECHNOLOGY LLC (SEAG-N); BOUTAGHOU Z (BOUT-I)
Inventor: BOUTAGHOU Z
Number of Countries: 094 Number of Patents: 009
Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week	
US 20020009949	A1	20020124	US 2000218262	P	20000713	200225	B
			US 2001901321	A	20010709		
WO 200207154	A2	20020124	WO 2001US21561	A	20010709	200225	
AU 200173273	A	20020130	AU 200173273	A	20010709	200236	
GB 2380049	A	20030326	WO 2001US21561	A	20010709	200323	
			GB 20031026	A	20030116		
US 6551173	B2	20030422	US 2000218262	P	20000713	200330	
			US 2001901321	A	20010709		
GB 2380049	B	20040107	WO 2001US21561	A	20010709	200404	
			GB 20031026	A	20030116		
KR 2003078057	A	20031004	KR 2003700501	A	20030113	200411	
JP 2004504685	W	20040212	WO 2001US21561	A	20010709	200413	
			JP 2002512974	A	20010709		
AU 2001273273	A8	20050915	AU 2001273273	A	20010709	200569	

Priority Applications (No Type Date): US 2000218262 P 20000713; US 2001901321 A 20010709
Patent Details:

Patent No	Kind	Lan	Pg	Main IPC	Filing Notes
US 20020009949	A1		12	B24B-049/00	Provisional application US 2000218262
WO 200207154	A2	E		G11B-005/00	
AU 200173273	A			G11B-005/00	Based on patent WO 200207154
GB 2380049	A			G11B-005/187	Based on patent WO 200207154
US 6551173	B2			B24B-001/00	Provisional application US 2000218262
GB 2380049	B			G11B-005/187	Based on patent WO 200207154
KR 2003078057	A			G11B-005/127	
JP 2004504685	W		31	G11B-005/60	Based on patent WO 200207154
AU 2001273273	A8			G11B-005/10	Based on patent WO 200207154

Designated States (National): AE AG AL AM AT AU AZ BA BB BG BR BY BZ CA CH CN CR CU CZ DE DK DM DZ EE ES FI GB GD GE GH GM HR HU ID IL IN IS JP KE KG KP KR KZ LC LK LR LS LT LU LV MA MD MG MK MN MW MX MZ NO NZ PL PT RO RU SD SE SG SI SK SL TJ TM TR TT TZ UA UG UZ VN YU ZA ZW
Designated States (Regional): AT BE CH CY DE DK EA ES FI FR GB GH GM GR IE IT KE LS LU MC MW MZ NL OA PT SD SE SL SZ TR TZ UG ZW

Abstract (Basic):
Technology Focus:
... control the approach of the front surface to the lapping surface. The applied pressures are **controlled** to adjust the **stripe height** of a **magnetoresistive transducer** or the throat height of an inductive transducer of each slider. The sliders are lapped...

7/3,K/8 (Item 5 from file: 350)
DIALOG(R)File 350:Derwent WPIX

014291946 **Image available**
WPI Acc No: 2002-112648/200215
XRPX Acc No: N02-083794
Electrical lapping guide for controlling stripe height **of** magnetoresistive **read** heads , **has resistive elements with upper edges away from lapping plane and relative to upper edge of giant magnetoresistive read sensor**

Patent Assignee: READ RITE CORP (READ-N)
Inventor: CRUE B W; HARNISCHFEGER M T; MACCHIONI C V; PLEWES S J; RUDY S C; SHEN Y
Number of Countries: 002 Number of Patents: 002
Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week	
US 6193584	B1	20010227	US 99321486	A	19990527	200215	B
JP 2001014617	A	20010119	JP 2000159237	A	20000529	200215	

Priority Applications (No Type Date): US 99321486 A 19990527
Patent Details:

Patent No	Kind	Lan	Pg	Main IPC	Filing Notes
US 6193584	B1		26	B24B-001/00	
JP 2001014617	A		23	G11B-005/39	

Electrical lapping guide for controlling stripe height **of** magnetoresistive **read** heads , **has resistive elements with upper edges away from lapping plane and relative to upper edge...**

Abstract (Basic):
... For **controlling stripe height** of **magnetoresistive** (**MR**) read **head** such as anisotropic **MR** read **heads** , giant **MR** read **heads** , spin valve read heads used in magnetic disk drives of computer

11/3,K/1 (Item 1 from file: 347)
DIALOG(R)File 347:JAPIO

07421462 **Image available**
NITRIDE SEMICONDUCTOR LASER ELEMENT

PUB. NO.: 2002-289972 [JP 2002289972 A]
PUBLISHED: October 04, 2002 (20021004)
INVENTOR(s): IWASA SHIGETO
YAMADA TAKAO
NAKAMURA SHUJI
APPLICANT(s): NICHIA CHEM IND LTD
APPL. NO.: 2002-006460 [JP 20026460]
Division of 08-053429 [JP 9653429]
FILED: March 11, 1996 (19960311)

INVENTOR(s): IWASA SHIGETO
YAMADA TAKAO
NAKAMURA SHUJI

ABSTRACT

... manufacturing a nitride semiconductor laser element, capable of easily manufacturing an active region at a **narrow stripe width** to thereby aim at a continuous oscillation at the ambient temperature by lowering the threshold...

11/3,K/2 (Item 2 from file: 347)
DIALOG(R)File 347:JAPIO

06515476 **Image available**
NITRIDE SEMICONDUCTOR LASER ELEMENT

PUB. NO.: 2000-101193 [JP 2000101193 A]
PUBLISHED: April 07, 2000 (20000407)
INVENTOR(s): KAWANO YOSHIHIRO
NAKAMURA SHUJI
APPLICANT(s): NICHIA CHEM IND LTD
APPL. NO.: 10-267759 [JP 98267759]
FILED: September 22, 1998 (19980922)

INVENTOR(s): KAWANO YOSHIHIRO
NAKAMURA SHUJI

ABSTRACT

... semiconductor laser element, with improved far field pattern and single vertical horizontal mode.

SOLUTION: A **stripe width** which is at least in a ridge shape is provided directly below and in parallel...

11/3,K/3 (Item 3 from file: 347)
DIALOG(R)File 347:JAPIO

06062531 **Image available**
NITRIDE SEMICONDUCTOR LASER ELEMENT AND MANUFACTURE THEREOF

PUB. NO.: 11-004039 [JP 11004039 A]
PUBLISHED: January 06, 1999 (19990106)
INVENTOR(s): YAMADA TAKAO
NAKAMURA SHUJI
APPLICANT(s): NICHIA CHEM IND LTD
APPL. NO.: 09-153814 [JP 97153814]
FILED: June 11, 1997 (19970611)

INVENTOR(s): YAMADA TAKAO
NAKAMURA SHUJI

ABSTRACT

...side clad layer 19 are partly etched into a ridge structure 4 μm in **stripe width** . In succession, a P electrode 21 of Ni and Au is formed on all the...

11/3,K/4 (Item 4 from file: 347)
DIALOG(R)File 347:JAPIO
(c) 2006 JPO & JAPIO. All rts. reserv.

05959481 **Image available**
NITRIDE SEMICONDUCTOR LASER ELEMENT

PUB. NO.: 10-242581 [JP 10242581 A]
PUBLISHED: September 11, 1998 (19980911)
INVENTOR(s): SANO MASAHIKO
NAKAMURA SHUJI
APPLICANT(s): NICHIA CHEM IND LTD [424878] (A Japanese Company or Corporation), JP (Japan)
APPL. NO.: 09-044176 [JP 9744176]
FILED: February 27, 1997 (19970227)

INVENTOR(s): SANO MASAHIKO
NAKAMURA SHUJI

ABSTRACT

...line (b) of the width of the active layer 3, the crystal of the ridge **stripe portion** 4' is made hardly destroyable, thereby improving the life time of the element.

11/3,K/5 (Item 5 from file: 347)
DIALOG(R)File 347:JAPIO
(c) 2006 JPO & JAPIO. All rts. reserv.

05791908 **Image available**
NITRIDE SEMICONDUCTOR LASER ELEMENT

PUB. NO.: 10-075008 [JP 10075008 A]
PUBLISHED: March 17, 1998 (19980317)
INVENTOR(s): SENOO MASAYUKI
NAKAMURA SHUJI
APPLICANT(s): NICHIA CHEM IND LTD [424878] (A Japanese Company or Corporation), JP (Japan)
APPL. NO.: 08-229161 [JP 96229161]
FILED: August 30, 1996 (19960830)

INVENTOR(s): SENOO MASAYUKI

NAKAMURA SHUJI

ABSTRACT

... 2. Meanwhile, over the entire flat surface of a p-type contact layer 8 of **stripe width** , a p-electrode 31 comprising Ni and Au is formed. By forming the n-electrode...

11/3,K/6 (Item 6 from file: 347)
DIALOG(R)File 347:JAPIO

05318914 **Image available**
NITRIDE SEMICONDUCTOR LASER ELEMENT

PUB. NO.: 08-274414 [JP 8274414 A]
PUBLISHED: October 18, 1996 (19961018)
INVENTOR(s): YAMADA TAKAO
SENOO MASAYUKI
NAKAMURA SHUJI
APPLICANT(s): NICHIA CHEM IND LTD [424878] (A Japanese Company or Corporation), JP (Japan)
APPL. NO.: 07-317846 [JP 95317846]
FILED: December 06, 1995 (19951206)

INVENTOR(s): YAMADA TAKAO
SENOO MASAYUKI
NAKAMURA SHUJI

ABSTRACT

... type contact layer 7. The positive electrode 12 having almost the same width as a **stripe width** of the p-type contact layer 7 etched to a stripe is formed in a...

11/3,K/7 (Item 7 from file: 347)
DIALOG(R)File 347:JAPIO

05258194 **Image available**
NITRIDE SEMICONDUCTOR LASER ELEMENT

PUB. NO.: 08-213694 [JP 8213694 A]
PUBLISHED: August 20, 1996 (19960820)
INVENTOR(s): SENOO MASAYUKI
YAMADA TAKAO
SUGIMOTO YASUNOBU
NAKAMURA SHUJI
APPLICANT(s): NICHIA CHEM IND LTD [424878] (A Japanese Company or Corporation), JP (Japan)
APPL. NO.: 07-020420 [JP 9520420]
FILED: February 08, 1995 (19950208)

INVENTOR(s): SENOO MASAYUKI
YAMADA TAKAO
SUGIMOTO YASUNOBU
NAKAMURA SHUJI

ABSTRACT

...the outside of the active layer of a nitride semiconductor laser element

by making the **stripe width** fo an N-type nitride semiconductor layer narrower than the width of a substrate...

... layers and loss is reduced, and oscillation is possible at all times. When the favorable **stripe width** (b) of the N-type nitride semiconductor layers is set in 1-50.mu.m...

11/3,K/8 (Item 8 from file: 347)
DIALOG(R)File 347:JAPIO

04909739 **Image available**
SEMICONDUCTOR LASER ELEMENT AND MANUFACTURE THEREOF

PUB. NO.: 07-202339 [JP 7202339 A]
PUBLISHED: August 04, 1995 (19950804)
INVENTOR(s): **OSAWA YASUHIRO**
APPLICANT(s): RICOH CO LTD [000674] (A Japanese Company or Corporation), JP (Japan)
APPL. NO.: 05-337404 [JP 93337404]
FILED: December 28, 1993 (19931228)

INVENTOR(s): **OSAWA YASUHIRO**

ABSTRACT

... clad layers 104, 105 and a cap layer 106 constitute the striped mesas whereby the **stripe width** of the fourth clad layer 104 is narrower than those of the fourth clad layer...

11/3,K/9 (Item 9 from file: 347)
DIALOG(R)File 347:JAPIO

04884226 **Image available**
GALLIUM NITRIDE COMPOUND SEMICONDUCTOR LASER ELEMENT

PUB. NO.: 07-176826 [JP 7176826 A]
PUBLISHED: July 14, 1995 (19950714)
INVENTOR(s): YAMADA TAKAO
SENOO MASAYUKI
NAKAMURA SHUJI
APPLICANT(s): NICHIA CHEM IND LTD [424878] (A Japanese Company or Corporation), JP (Japan)
APPL. NO.: 05-318275 [JP 93318275]
FILED: December 17, 1993 (19931217)

INVENTOR(s): YAMADA TAKAO
SENOO MASAYUKI
NAKAMURA SHUJI

ABSTRACT

...etching is performed until the layer 3 is exposed to form a waveguide of a **stripe width** formed in a width of 50.mu.m. After the etching, the mask is peeled...

11/3,K/10 (Item 10 from file: 347)
DIALOG(R)File 347:JAPIO

03695583 **Image available**
ASSEMBLING METHOD FOR IMAGE FORMING DEVICE

PUB. NO.: 04-060683 [JP 4060683 A]
PUBLISHED: February 26, 1992 (19920226)
INVENTOR(s): YAGI MICHIO
NAGAI MASARU
TSUTSUMI TAKASHI
SUGAYA TOYOAKI
HANEDA SATORU
APPLICANT(s): KONICA CORP [000127] (A Japanese Company or Corporation), JP (Japan)
APPL. NO.: 02-172135 [JP 90172135]
FILED: June 29, 1990 (19900629)
JOURNAL: Section: P, Section No. 1368, Vol. 16, No. 256, Pg. 4, June 10, 1992 (19920610)

INVENTOR(s): YAGI MICHIO
NAGAI MASARU
TSUTSUMI TAKASHI
SUGAYA TOYOAKI
HANEDA SATORU

ABSTRACT

... deviation in the breadthwise direction of a belt photosensitive body by positioning rolls to projecting **stripe zones** of the belt photosensitive body and circulating the belt photosensitive belt by preparatory rotation of rolls to completely move the belt photosensitive body to projecting **stripe zones** after assembling the belt photosensitive body in a device main body...

...CONSTITUTION: Projecting **stripe zones** 301 and 302 projecting to the inside are formed on the peripheral edge of a belt photosensitive body 3, and rolls 1 and 2 are positioned to projecting **stripe zones** 301 and 302. After the belt photosensitive body 3 is assembled in the device main ...

... circulated by preparatory rotation of rolls 1 and 2 and is completely moved to projecting **stripe zones** 301 and 302. Since the belt photosensitive body 3 is already completely moved to one..

13/3,K/1 (Item 1 from file: 347)
DIALOG(R)File 347:JAPIO

06602015 **Image available**
THIN-FILM MAGNETIC HEAD

PUB. NO.: 2000-187812 [JP 2000187812 A]
PUBLISHED: July 04, 2000 (20000704)
INVENTOR(s): NAKAMURA MASAHIRO
SASAKURI KOZO
HIGUCHI TAKAHIRO
NAGAI HIDEYASU
HASHIMOTO MASAYA
TAKAGISHI MASAYUKI
APPLICANT(s): READ RITE SMI KK
APPL. NO.: 10-359337 [JP 98359337]
FILED: December 17, 1998 (19981217)

ABSTRACT
...the thermal stability and EDS durability of a spin valve element.

SOLUTION: A thin-film **magnetic head** is equipped with a bottom type spin valve element 9 constituted by **stacking** an antiferromagnetic body layer 91, a fixed-side magnetic body layer 92, a nonmagnetic conductor layer 93 and a free-side magnetic body **layer** 94 on a **substrate** in this order, and a couple of electrode layers which are connected to both ends of the element 9. The thin-film **magnetic head** has its internal end surface tapered in its **stripe height** direction so that the **stripe height** SHAFM of the element 9 gradually increases from the upper end side to the lower...

13/3,K/2 (Item 2 from file: 347)
DIALOG(R)File 347:JAPIO

06596425 **Image available**
MAGNETORESISTIVE MAGNETIC HEAD

PUB. NO.: 2000-182222 [JP 2000182222 A]
PUBLISHED: June 30, 2000 (20000630)
INVENTOR(s): NAKAMURA MASAHIRO
SASAKURI KOZO
HIGUCHI TAKAHIRO
NAGAI HIDEYASU
HASHIMOTO MASAYA
TAKAGISHI MASAYUKI
APPLICANT(s): READ RITE SMI KK
APPL. NO.: 10-359336 [JP 98359336]
FILED: December 17, 1998 (19981217)

ABSTRACT

PROBLEM TO BE SOLVED: To improve the thermal stability and ESD durability of an **MR head** .

SOLUTION: In this **magnetoresistive magnetic head** provided with a thin-film **magneto** -resistance **element** 9, a couple of electrode layers which are electrically connected to the right and left ends of the element

9, and shield layers 7 and 12 which are **stacked** on the top and reverse sides of the thin-film **magneto** - resistance **element** 9 and electrode layer 10 across gap layers 9 and 11, a thermal buffer film...

... materials of the gap layers 8 and 11 is formed adjacently inside the thin-film **magneto** -resistance **element** 9 in the direction of **stripe height** SH.

13/3,K/3 (Item 1 from file: 350)
DIALOG(R)File 350:Derwent WPIX

017443212 **Image available**
WPI Acc No: 2005-766891/200578
XRAM Acc No: C05-234583
XRPX Acc No: N05-633104
Current perpendicular to plane magnetoresistive sensor for perpendicular recording systems, comprises pinning structure between backward extending portions of pinned layer structures
Patent Assignee: HITACHI GLOBAL STORAGE TECHNOLOGIES NETH (HITA-N)
Inventor: GILL H S
Number of Countries: 001 Number of Patents: 001
Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week	
US 20050243474	A1	20051103	US 2004837192	A	20040430	200578	B

Priority Applications (No Type Date): US 2004837192 A 20040430
Patent Details:

Patent No	Kind	Lan	Pg	Main IPC	Filing Notes
US 20050243474	A1		14	G11B-005/33	

Abstract (Basic):
... structures and the free layer forming a sensor stack having a back edge defining a **stripe height** measured perpendicular to the ABS, each pinned layer structure having a backward extending portion extending beyond the **stripe height** of sensor **stack** ; and pinning structure between backward extending portions of the pinned layer structures...

13/3,K/4 (Item 2 from file: 350)
DIALOG(R)File 350:Derwent WPIX

015394445 **Image available**
WPI Acc No: 2003-456586/200343
XRPX Acc No: N03-363102
Magnetoresistive reader formation method involves defining stripe height back edge of magnetoresistive sensor prior to defining reader width of sensor
Patent Assignee: SEAGATE TECHNOLOGY LLC (SEAG-N)
Inventor: ANDERSON P E; BURBANK D P; DIMITROV D V; JIN I; LARSON R P; NAUGHTON K P
Number of Countries: 001 Number of Patents: 001
Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week	
US 20030046807	A1	20030313	US 2001322311	P	20010912	200343	B

US 200250236 A 20020115

Priority Applications (No Type Date): US 2001322311 P 20010912; US 200250236 A 20020115
Patent Details:
Patent No Kind Lan Pg Main IPC Filing Notes
US 20030046807 A1 17 G11B-005/127 Provisional application US 2001322311
Abstract (Basic):
... of sensor. Stripe height back edge and reader width of sensor are defined by depositing **multiple magnetoresistive sensor layers** , selectively patterning photoresist layer that leaves a region of sensor layer exposed and removing the...

File 348:EUROPEAN PATENTS 1978-2006/Feb W03
(c) 2006 European Patent Office
File 349:PCT FULLTEXT 1979-2006/UB=20060216,UT=20060209
(c) 2006 WIPO/Univentio

Set	Items	Description
S1	10031	(MAGNET? OR MR OR GMR OR GIANT()MAGNETORESISTANCE)(3N)(HEAD?? OR ELEMENT?? OR SENSOR?? OR SENSING OR SENSITIVE OR ACTIVE OR TRANSDUCER??)
S2	1469	STRIPE??()(WIDTH?? OR HEIGHT OR AREA?? OR SIZE?? OR VOLUME?? OR DEPTH OR PORTION?? OR REGION?? OR ZONE??)
S3	156	(CONTROL? OR CHANGE?? OR CHANGING OR WIDEN??? OR NARROW??? OR MODIFY??? OR MODIFY? OR REDUCE?? OR REDUCING OR SHRINK???)(3N)S2
S4	263948	STACK??? OR (PLURAL? OR MANY OR MULTIPLE?? OR MANY OR SEVERAL OR MULTI OR NUMEROUS OR SUBSTRATE)(3N)LAYER??
S5	1451	AU=(HANEDA, S? OR HANEDA S? OR OSAWA, Y? OR OSAWA Y? OR NAKAMURA, S? OR NAKAMURA S?)
S6	2267	(GATE()ELECTRODE??)(3N)VOLT????
S7	17	S1(3N)S2
S8	0	S7(3N)S4
S9	0	S7(3N)S6
S10	0	S7 AND S5
S11	7	S2 AND S5
S12	17	S7 NOT S11
S13	16	S12 AND IC=G11B?
S14	0	S11 AND IC=G11B?
S15	2	S1(3N)S3
S16	0	S15 NOT (S7 OR S11)
S17	0	(S2 OR S3)(3N)S6

11/3,K/1 (Item 1 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

01264764
Semiconductor device, semiconductor substrate, and manufacture method
Halbleitervorrichtung, Halbleitersubstrat und Herstellungsverfahren
Dispositif semi-conducteur, Substrat semi-conducteur et procede de fabrication
PATENT ASSIGNEE:
Matsushita Electronics Corporation, (456138), 1-1, Saiwai-cho, Takatsuki-shi, Osaka 569-1193, (JP), (Applicant designated States: all)
INVENTOR:
Nakamura, Shinji , 1-3-507-403, Nasahara, Takatsuki-shi, Osaka 569-1041, (JP)
Ishida, Masahiro, 24-6, Ikaga-nishimachi, Hirakata-shi, Osaka 573-0066, (JP)
Orita, Kenji, 1-44-9, Tsunoe-cho, Takatsuki-shi, Osaka 569-0822, (JP)
Imafuji, Osamu, 1-10-5-507, Kamihamuro-cho, Takatsuki-shi, Osaka 569-1044, (JP)
Yuri, Masaaki, 6-26-1201, Funaki-cho, Ibaraki-shi, Osaka 567-0828, (JP
LEGAL REPRESENTATIVE:
Grunecker, Kinkeldey, Stockmair & Schwanhausser Anwaltssozietat (100721), Maximilianstrasse 58, 80538 Munchen, (DE)
PATENT (CC, No, Kind, Date): EP 1091422 A2 010411 (Basic)
APPLICATION (CC, No, Date): EP 121878 001006;
PRIORITY (CC, No, Date): JP 99285582 991006
DESIGNATED STATES: AT; BE; CH; CY; DE; DK; ES; FI; FR; GB; GR; IE; IT; LI; LU; MC; NL; PT; SE
EXTENDED DESIGNATED STATES: AL; LT; LV; MK; RO; SI
INTERNATIONAL PATENT CLASS (V7): H01L-033/00; H01L-021/20
ABSTRACT WORD COUNT: 52
NOTE:
Figure number on first page: 1

LANGUAGE (Publication,Procedural,Application): English; English; English
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS A	(English)	200115	2146
SPEC A	(English)	200115	9769
Total word count - document A			11915
Total word count - document B			0
Total word count - documents A + B			11915

INVENTOR:
Nakamura, Shinji ...

...SPECIFICATION the depressions or projections are placed. As a result of such arrangement, defects in the **stripe region** can be reduced, thereby improving the characteristics of the semiconductor laser elements.

EMBODIMENT 5
Referring...

11/3,K/2 (Item 2 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

01206566
NITRIDE SEMICONDUCTOR LASER ELEMENT
NITRIDHALBLEITERLASERELEMENT
ELEMENT DE LASER SEMICONDUCTEUR AU NITRURE

PATENT ASSIGNEE:
Nichia Corporation, (2966640), 491-100, Oka, Kaminaka-cho, Anan-shi, Tokushima 774-8601, (JP), (Applicant designated States: all)
INVENTOR:
KOZAKI, Tokuya Nichia Corporation, 491-100, Oka, Kaminakacho, Anan-shi Tokushima 774-8601, (JP)
SANO, Masahiko Nichia Corporation, 491-100, Oka, Kaminakacho, Anan-shi Tokushima 774-8601, (JP)
NAKAMURA, Shuji Nichia Corporation , 491-100, Oka, Kaminakacho, Anan-shi Tokushima 774-8601, (JP)
NAGAHAMA, Shinichi Nichia Corporation, 491-100, Oka, Kaminakacho, Anan-shi Tokushima 774-8601, (JP
LEGAL REPRESENTATIVE:
VOSSIUS & PARTNER (100314), Siebertstrasse 4, 81675 Munchen, (DE)
PATENT (CC, No, Kind, Date): EP 1168539 A1 020102 (Basic)
WO 200052796 000908
APPLICATION (CC, No, Date): EP 2000906695 000303; WO 2000JP1308 000303
PRIORITY (CC, No, Date): JP 9957211 990304; JP 99157646 990604; JP 99163499 990610; JP 99163500 990610
DESIGNATED STATES: AT; BE; CH; CY; DE; DK; ES; FI; FR; GB; GR; IE; IT; LI; LU; MC; NL; PT; SE
INTERNATIONAL PATENT CLASS (V7): H01S-005/22
ABSTRACT WORD COUNT: 193
NOTE:
Figure number on first page: 11

LANGUAGE (Publication,Procedural,Application): English; English; Japanese
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS A	(English)	200201	1160
SPEC A	(English)	200201	26724
Total word count - document A			27884
Total word count - document B			0
Total word count - documents A + B			27884

INVENTOR:
... JP)
NAKAMURA, Shuji Nichia Corporation ...

...ABSTRACT stripe structure formed by etching from the side of the p-side contact layer. The **stripe width** provided by etching is within the stripe range of 1 to 3 (mu)m and...

...SPECIFICATION from the p-side contact layer to above the active layer, characterized in that the **stripe width** providing by etching is within the narrow stripe range of 1 to 3 (mu)m...

...0.1 (mu)m.
That is, according to the present invention, the waveguide having such **stripe width** and depth enables the basic mode emission having a stable lateral mode and there is...

...the device having less leak current and a high reliability can be obtained.
Preferably, the **stripe width** is 1.2 to 2 (mu)m. This nitride semiconductor device has a refractive index...In the ridge waveguide

structure, the effective refractive index changes depending on the etching depth, **stripe height** and the like. Such a structure change effects on the device properties extremely. Then, the...

...the aspect ratio is about 2.0 and moreover, about 1.5.

And since the **stripe width** of the projection part is within the range of not less than 1 (mu)m...the dispersion of devices is small and the yield of manufacture can be increased.

The **stripe width** of the projection part is preferably not less than 1 (mu)m and not more...an example of the present invention.

Fig. 7 is a diagram showing the relation between **stripe width** and single transverse mode oscillation in the present invention.

Fig. 8 is a diagram showing...oxide is preferably used as a material that can be easily dissolved in hydrofluoric acid. **Stripe width** (W) of the first protective film is controlled within a range from 3 (mu)m to 1 (mu)m. **Stripe width** of the first protective film 61 corresponds substantially to the **stripe width** in the waveguide region.

Figs.3A and 3B show specific processes of forming the first...to restrict the formation of the p electrode only on the contact layer of small **stripe width** and, instead, the p electrode may be formed over a large area. In addition, an...the present invention, satisfactory control of the transverse mode is made possible by setting the **stripe width** of the ridge waveguide, or the **stripe width** of the protruding portion of the p-side optical guide layer in a range from...the present invention, satisfactory control of the transverse mode is made possible by setting the **stripe width** of the ridge waveguide, or the **stripe width** of the protruding portion of the p-side optical guide layer, in a range from...protective film 61 and a third protective film 63 made of photo resist having a **stripe width** of 2 (mu)m and a thickness of 1 (mu)m was formed.

Next, as...

...by the treatment with an etchant to form a first protective film 61 having a **stripe width** of 2 (mu)m on the p-side contact layer 13, as shown in Fig 13. The p-electrode 20 had a **stripe width** of 100 (mu)m and was formed in a manner to extend over the second...this drawing, the layered structure which is cut in the perpendicular direction to the projected **stripe region** is shown. Example 7 will be described with reference to Fig. 17.

A sapphire substrate...protective film 161 and a third protective film 163 made of photo resist having a **stripe width** of 2 (mu)m and a thickness of 1 (mu)m was formed. The insulting...

...by the treatment with an etchant to form a first protective film 161 having a **stripe width** of 2 (mu)m on the p-side contact layer 112, as shown in Fig...

...film 161 on said p-side contact layer 112. The p-electrode 120 had a **stripe width** of 100 (mu)m and was formed in a manner to extend over the second...laser device was fabricated in the same manner as in Example 7, except that the **stripe width** of the p-side optical waveguide layer was 3 (mu)m. For the resulting laser...devices in which kinks occurred was increased as compared with in Example 7. Thus, the **stripe width** is more preferably in the range of 2 (mu)m (+-) 0.5 (mu)m (between...this drawing, the layered structure which is cut in the perpendicular direction to the projected **stripe region** is shown. Example 13 will be described with reference to Fig. 18.

A sapphire substrate...protective film 161 and a third protective film 163 made of photo resist having a **stripe width** of 2 (mu)m and a thickness of 1 (mu)m was formed. The insulting...

...by the treatment with an etchant to form a first protective film 161 having a **stripe width** of 2 (mu)m on the p-side contact layer 112, as shown in Fig...film 161 on said p-side contact layer 112. The p-electrode 120 had a **stripe width** of 100 (mu)m and was formed in a manner to extend over the second...laser device was fabricated in the same manner as in Example 13, except that the **stripe width** of the projected portion of the p-side optical waveguide layer, that is, the width...

...the ratio of the defective devices in which kinks occurred tended to increase. Therefore, the **stripe width** is more preferably within the range of 2 (mu)m (+-) 0.5 (mu)m (between...Table 4 were laminated sequentially on the substrate. Next, The stripe ridge waveguide having a **stripe width** of 1.8 (mu)m was formed by etching from the p-side contact layer...

11/3,K/3 (Item 3 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

01199269
NITRIDE SEMICONDUCTOR DEVICE AND ITS MANUFACTURINO METHOD
NITRIDHALBLEITER UND SEINE HERSTELLUNGSMETHODE
SEMI-CONDUCTEUR AU NITRURE ET PROCEDE DE FABRICATION
PATENT ASSIGNEE:
Nichia Corporation, (2966640), 491-100, Oka, Kaminaka-cho, Anan-shi, Tokushima 774-8601, (JP), (Applicant designated States: all)
INVENTOR:
NAGAHAMA, Shinichi Nichia Corporation, 491-100, Oka, Kaminakacho, Anan-shi Tokushima 774-8601, (JP)
NAKAMURA, Shuji Nichia Corporation , 491-100, Oka, Kaminakacho, Anan-shi Tokushima 774-8601, (JP
LEGAL REPRESENTATIVE:
OK pat AG (101251), Chamerstrasse 50, 6300 Zug, (CH)
PATENT (CC, No, Kind, Date): EP 1184913 A1 020306 (Basic)
WO 200048254 000817
APPLICATION (CC, No, Date): EP 2000902126 000208; WO 2000JP660 000208
PRIORITY (CC, No, Date): JP 9930990 990209; JP 99331797 991122
DESIGNATED STATES: AT; BE; CH; CY; DE; DK; ES; FI; FR; GB; GR; IE; IT; LI; LU; MC; NL; PT; SE
EXTENDED DESIGNATED STATES: AL; LT; LV; MK; RO; SI
INTERNATIONAL PATENT CLASS (V7): H01L-033/00; H01L-021/205; H01S-005/323
ABSTRACT WORD COUNT: 79
NOTE:
Figure number on first page: 5

LANGUAGE (Publication,Procedural,Application): English; English; Japanese
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS A	(English)	200210	296
SPEC A	(English)	200210	5904
Total word count - document A			6200
Total word count - document B			0
Total word count - documents A + B			6200

INVENTOR:
... JP)
NAKAMURA, Shuji Nichia Corporation ...

...SPECIFICATION mask having stripes was formed. Then, the SiO2)) film which was patterned to have a **stripe width** (the upper part of the convex portion) of 5 (mu)m and a stripe distance...protective film 61 and a third protective film 63 made of photo resist having a **stripe width** of 1.8 (mu)m and a thickness of 1 (mu)m was formed.
Next...

...by the treatment with an etchant to form a first protective film 61 having a **stripe width** of 1.8 (mu)m on the p-side contact layer 10, as shown in...

...again etched using SiCl4)) gas with the RIE to form a ridge stripe having a **stripe width** of 1.8 (mu)m.
After formation of the ridge stripe, the wafer was transferred...

...protective film 61 on said p-side contact layer. The p-electrode 20 had a **stripe width** of 100 (mu)m and was formed in a manner to extend over the

11/3,K/4 (Item 4 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

01026054
NITRIDE SEMICONDUCTOR DEVICE
HALBLEITERVORRICHTUNG AUS EINER NITRIDVERBINDUNG
DISPOSITIF A SEMI-CONDUCTEUR EN NITRURE
PATENT ASSIGNEE:
NICHIA CHEMICAL INDUSTRIES, LTD., (1569971), 491-100, Oka, Kaminakacho, Anan-shi, Tokushima 774-8601, (JP), (Applicant designated States: all)
INVENTOR:
NAKAMURA, Shuji, Nichia Chemical Industries, Ltd. , 491-100, Oka, Kaminakacho, Anan-shi, Tokushima 774-8601, (JP)
MUKAI, Takashi, Nichia Chemical Industries, Ltd., 491-100, Oka, Kaminakacho, Anan-shi, Tokushima 774-8601, (JP)
TANIZAWA, Koji, Nichia Chemical Industries, Ltd., 491-100, Oka, Kaminakacho, Anan-shi, Tokushima 774-8601, (JP)
MITANI, Tomotsugu, Nichia Chemical Industries, Ltd, 491-100, Oka, Kaminakacho, Anan-shi, Tokushima 774-8601, (JP)
MARUI, Hiromitsu, Nichia Chemical Industries, Ltd., 491-100, Oka, Kaminakacho, Anan-shi, Tokushima 774-8601, (JP
LEGAL REPRESENTATIVE:
OK pat AG (101251), Chamerstrasse 50, 6300 Zug, (CH)
PATENT (CC, No, Kind, Date): EP 1014455 A1 000628 (Basic)
WO 9905728 990204
APPLICATION (CC, No, Date): EP 98933944 980727; WO 98JP3336 980727
PRIORITY (CC, No, Date): JP 97199471 970725; JP 97235524 970901; JP 97286304 971020; JP 97304328 971106; JP 97317421 971118; JP 97348972 971218; JP 97348973 971218; JP 98176623 980608; JP 98176634 980608; JP 98199829 980629
DESIGNATED STATES: DE; ES; FR; GB; IT; NL; SE
INTERNATIONAL PATENT CLASS (V7): H01L-033/00
ABSTRACT WORD COUNT: 89
NOTE:
Figure number on first page: 01

LANGUAGE (Publication,Procedural,Application): English; English; Japanese
FULLTEXT AVAILABILITY:
Available Text Language Update Word Count

CLAIMS A (English) 200026 630
SPEC A (English) 200026 11708
Total word count - document A 12338
Total word count - document B 0
Total word count - documents A + B 12338

INVENTOR:
NAKAMURA, Shuji, Nichia Chemical Industries, Ltd ...

...SPECIFICATION are the uppermost layers are etched with RIE apparatus into a ridge geometry with a **stripe width** 4 (mu)m.
After the ridge geometry is formed, as shown in Fig. 2, the...are the uppermost layers are etched with RIE apparatus into a ridge geometry with a **stripe width** 4 (mu)m. Particularly, when the nitride semiconductor layers containing Al which are above the...

11/3,K/5 (Item 5 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

01002261
METHOD OF GROWING NITRIDE SEMICONDUCTORS, NITRIDE SEMICONDUCTOR SUBSTRATE AND NITRIDE SEMICONDUCTOR DEVICE
WACHSTUMSMETHODE FUR EINEN NITRID-HALBLEITER, NITRID HALBLEITERSUBSTRAT UND VORRICHTUNG
PROCEDE ASSURANT LA CROISSANCE DE SEMI-CONDUCTEURS DE NITRURE, SUBSTRAT SEMI-CONDUCTEUR DE NITRURE ET DISPOSITIF SEMI-CONDUCTEUR AU NITRURE.
PATENT ASSIGNEE:
NICHIA CHEMICAL INDUSTRIES, LTD., (1569971), 491-100, Oka, Kaminakacho, Anan-shi, Tokushima 774-8601, (JP), (Applicant designated States: all)
INVENTOR:
KIYOKU, Hiroyuki-Nichia Chemical Industries, Ltd., 491-100, Oka,Kaminaka-cho,Anan-shi, Tokushima-ken 774-0044, (JP)
NAKAMURA, Shuji-Nichia Chemical Industries, Ltd. , 491-100, Oka,Kaminaka-cho,Anan-shi, Tokushima-ken 774-0044, (JP)
KOZAKI, Tokuya-Nichia Chemical Industries, Ltd., 491-100, Oka,Kaminaka-cho,Anan-shi, Tokushima-ken 774-0044, (JP)
IWASA, Naruhito-Nichia Chemical Industries, Ltd., 491-100, Oka,Kaminaka-cho,Anan-shi, Tokushima-ken 774-0044, (JP)
CHOCHO, Kazuyuki-Nichia Chemical Industries, Ltd., 491-100, Oka,Kaminaka-cho,Anan-shi, Tokushima-ken 774-0044, (JP
LEGAL REPRESENTATIVE:
Hertz, Oliver, Dr. (79051), v. Bezold & Partner, Patentanwalte Akademiestrasse 7, 80799 Munchen, (DE)
PATENT (CC, No, Kind, Date): EP 942459 A1 990915 (Basic)
WO 9847170 981022
APPLICATION (CC, No, Date): EP 98912742 980409; WO 98JP1640 980409
PRIORITY (CC, No, Date): JP 9793315 970411; JP 97174494 970630; JP 97181071 970707; JP 97201477 970728; JP 97277448 971009; JP 97290098 971022; JP 97324997 971126
DESIGNATED STATES: AT; BE; CH; CY; DE; DK; ES; FI; FR; GB; GR; IE; IT; LI; LU; MC; NL; PT; SE
INTERNATIONAL PATENT CLASS (V7): H01L-021/205; H01L-033/00; C23C-016/34
ABSTRACT WORD COUNT: 137
NOTE:
Figure number on first page: 1C

LANGUAGE (Publication,Procedural,Application): English; English; Japanese
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS A	(English)	9937	5636
SPEC A	(English)	9937	28314
Total word count - document A			33950
Total word count - document B			0
Total word count - documents A + B			33950

INVENTOR:
... JP)
NAKAMURA, Shuji-Nichia Chemical Industries, Ltd ...

...SPECIFICATION 1-(mu)m thick selective growth masks 13 made of many SiO2)) stripes having a **stripe width** of 10 (mu)m and a stripe interval (width of each window) of 6 (mu...described with reference to FIGS. 6A to 6C.

Second selective growth masks 113 having a **stripe width** of 10 (mu)m and a stripe interval of 6 (mu)m were grown on...

...layer structure. First selective growth masks 13 made up of many SiO2)) stripes having a **stripe width** of 10 (mu)m and a stripe interval of 8 (mu)m were grown on...

...lapping. Second selective growth masks 113 made up of many Si3))N4)) stripes having a **stripe width** of 12 (mu)m and a stripe interval of 6 (mu)m were grown on...this spinnel substrate 11 to extend in a direction perpendicular to the ORF surface. The **stripe width** was 12 (mu)m, and the stripe interval was 6 (mu)m.

A quartz boat...tow-layer structure. First selective growth masks made up of many SiO2)) stripes having a **stripe width** of 20 (mu)m and a stripe interval of 5 (mu)m were grown on...

...structure. Thereafter, first selective growth masks 13 made up of many SiO2)) stripes having a **stripe width** of 25 (mu)m and a stripe interval of 5 (mu)m were grown on...

...m thick second selective growth masks made up of silicon dioxide stripes, each having a **stripe width** of 15 (mu)m, were formed at positions corresponding to the window portions of the...the underlayer 12. Selective growth masks 13 made up of many SiO2)) stripes having a **stripe width** of 20 (mu)m and a stripe interval (width of each window) of 5 (mu...1, and first selective growth masks 13 made up of many SiO2)) stripes having a **stripe width** of 10 (mu)m and a stripe interval (window 14) of 5 (mu)m were...m thick first selective growth masks 13 made up of many SiO2)) stripes having a **stripe width** of 10 (mu)m and a stripe interval of 3 (mu)m were formed on...layer 218 were etched by using the RIE apparatus to provide a ridge having a **stripe width** of 4 (mu)m. A p-side electrode 220 having a two-layer structure made...on the resultant structure in the same manner as in Example 10 except that the **stripe width** was 10 (mu)m and the stripe interval was 5 (mu)m.

This wafer was...m thick first selective growth masks 13 made up of many SiO2)) stripes having a **stripe width** of 10 (mu)m and a stripe interval of 2 (mu)m were formed on...

...and the p-side cladding layer 218 were etched to provide a ridge having a **stripe width** of 4 (mu)m by using the RIE apparatus. At this time, ridge stripes were...m thick first selective growth masks 13 made up of many SiO2)) stripes having a **stripe width** of 10 (mu)m and a stripe interval of 2 (mu)m were formed on...on the GaN layer 71, and 1-(mu)m thick silicon dioxide stripes having a **stripe width** of 15 (mu)m and a stripe interval of 3 (mu)m were formed by...

11/3,K/6 (Item 6 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

00975695
NITRIDE SEMICONDUCTOR DEVICE
HALBLEITERANORDNUNG AUS EINER NITRIDVERBINDUNG
DISPOSITIF A SEMI-CONDUCTEUR AU NITRURE
PATENT ASSIGNEE:
NICHIA CHEMICAL INDUSTRIES, LTD., (1569971), 491-100, Oka, Kaminakacho, Anan-shi, Tokushima 774-8601, (JP), (Applicant designated States: all)
INVENTOR:
NAGAHAMA, Shinichi, Nichia Chemical Ind., Ltd., 491-100, Oka, Kaminakacho , Anan-shi, Tokushima 774, (JP)
SENOH, Masayuki, Nichia Chemical Industries, Ltd., 491-100, Oka, Kaminakacho, Anan-shi, Tokushima 774, (JP)
NAKAMURA, Shuji, Nichia Chemical Industries, Ltd. , 491-100, Oka, Kaminakacho, Anan-shi, Tokushima 774, (JP
LEGAL REPRESENTATIVE:
OK pat AG (101251), Chamerstrasse 50, 6300 Zug, (CH)
PATENT (CC, No, Kind, Date): EP 1017113 A1 000705 (Basic)
WO 9831055 980716
APPLICATION (CC, No, Date): EP 98900171 980108; WO 98JP25 980108
PRIORITY (CC, No, Date): JP 971937 970109; JP 9712707 970127; JP 97102793 970403; JP 97134210 970526; JP 97244342 970909; JP 97274438 971007; JP 97311272 971027
DESIGNATED STATES: AT; BE; CH; DE; DK; ES; FI; FR; GB; GR; IE; IT; LI; LU; MC; NL; PT; SE
INTERNATIONAL PATENT CLASS (V7): H01L-033/00; H01S-003/18
ABSTRACT WORD COUNT: 95
NOTE:
Figure number on first page: 1

LANGUAGE (Publication,Procedural,Application): English; English; Japanese
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS A	(English)	200027	3816
SPEC A	(English)	200027	36342
Total word count - document A			40158
Total word count - document B			0
Total word count - documents A + B			40158

INVENTOR:
... JP)
NAKAMURA, Shuji, Nichia Chemical Industries, Ltd ...

...SPECIFICATION cladding layer are etched with the RIE apparatus to form a ridge geometry having a **stripe width** of 4 (mu)m, as shown in Fig. 9. When the ridge stripe is formed...layer 19 were etched with RIE apparatus to make them a ridge geometry having a **stripe width** of 4 (mu)m.
Next, a mask was formed on the surface of the ridge...layer 20 and p-side cladding layer were etched into a ridge-geometry with a **stripe width** of 4 (mu)m with the RIE apparatus.
Next, in the same manner as in...side cladding layer 19 were etched with RIE apparatus into a ridge geometry with a **stripe width** of 4 (mu)m. Thus, since the layers above the active layer were made to...layer 20 and p-side cladding layer were etched into a ridge geometry with a **stripe width** of 4 (mu)m.

After forming a ridge, a stripe p-electrode 21 consisting of...layer and the p-side cladding layer were etched into a ridge geometry with a **stripe width** of 4 (mu)m. Thus, the layers above the active layer had a stripe ridge...layer and the p-side cladding layer 317 were etched into a ridge having a **stripe width** of 4 (mu)m, as shown in Fig. 9, with a RIE apparatus. When the...

11/3,K/7 (Item 7 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

00858462
Electro-absorption optical modulator
Elektroabsorptionsmodulator
Modulateur du type a electro-absorption
PATENT ASSIGNEE:
MATSUSHITA ELECTRIC INDUSTRIAL CO., LTD., (216883), 1006, Oaza-Kadoma, Kadoma-shi, Osaka 571-8501, (JP), (Proprietor designated states: all)
INVENTOR:
Nakamura, Shinji , 1-4-14, Asukano-minami, Ikoma-shi, Nara-ken, (JP)
Kamiyama, Satoshi, 5-4-3-905, Hazamagaoka, Sanda-shi, Hyogo-ken, (JP)
Matsuda, Kenichi, 3-11-15-717, Yagumokita-machi, Moriguchi-shi, Osaka, (JP)
Matsui, Yasushi, 8-23, Kansozuka-cho, Neyagawa-shi, Osaka, (JP
LEGAL REPRESENTATIVE:
Kugele, Bernhard et al (51541), NOVAPAT INTERNATIONAL SA, 9, Rue du Valais, 1202 Geneve, (CH)
PATENT (CC, No, Kind, Date): EP 790521 A1 970820 (Basic)
EP 790521 B1 010816
APPLICATION (CC, No, Date): EP 97102201 970212;
PRIORITY (CC, No, Date): JP 9624952 960213
DESIGNATED STATES: DE; FR; GB; IT; NL
INTERNATIONAL PATENT CLASS (V7): G02F-001/015
NOTE:
Figure number on first page: 3A 3B
LANGUAGE (Publication,Procedural,Application): English; English; English
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS A	(English)	199708W3	594
CLAIMS B	(English)	200133	592
CLAIMS B	(German)	200133	555
CLAIMS B	(French)	200133	674
SPEC A	(English)	199708W3	5006
SPEC B	(English)	200133	5115
Total word count - document A			5601
Total word count - document B			6936
Total word count - documents A + B			12537

INVENTOR:
Nakamura, Shinji ...

...SPECIFICATION and/or an impurity concentration of the semiconductor layers, a shape of the waveguide, the **stripe width** of the ridge portion, or the like) may be offset from the intended design value...

...SPECIFICATION and/or an impurity concentration of the semiconductor layers, a shape of the waveguide, the **stripe width** of the ridge portion, or the like) may be offset from the intended design value...

13/3,K/1 (Item 1 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS
(c) 2006 European Patent Office. All rts. reserv.

02025061
Method of manufacturing magnetic heads with reference and monitoring lapping guides
Herstellungsverfahren fur Magnetkopfe mittels Referenz- und Uberwachungseinschleiffuhrung
Procede de fabrication de tetes magnetiques utilisant des guides de rodage de reference et de controle
PATENT ASSIGNEE:
QUANTUM CORPORATION, (567674), 1650 Technology Drive, Suite 800, San Jose,California 95110, (US), (Applicant designated States: all)
INVENTOR:
Wu, Andrew L., 15 High Street, ShrewsburyMassachusetts 01545, (US)
LEGAL REPRESENTATIVE:
Charig, Raymond Julian (79692), Eric Potter Clarkson, Park View House, 58 The Ropewalk, Nottingham NG1 5DD, (GB)
PATENT (CC, No, Kind, Date): EP 1626392 A1 060215 (Basic)
APPLICATION (CC, No, Date): EP 2005255020 050812;
PRIORITY (CC, No, Date): US 917782 040813
DESIGNATED STATES: AT; BE; BG; CH; CY; CZ; DE; DK; EE; ES; FI; FR; GB; GR; HU; IE; IS; IT; LI; LT; LU; LV; MC; NL; PL; PT; RO; SE; SI; SK; TR
EXTENDED DESIGNATED STATES: AL; BA; HR; MK; YU
INTERNATIONAL CLASSIFICATION (V8 + ATTRIBUTES):
IPC + Level Value Position Status Version Action Source Office:
G11B-0005/31 A I F B 20060101 20051128 H EP
G11B-0005/39 A I L B 20060101 20051128 H EP
B24B-0049/04 A I L B 20060101 20051128 H EP
B24B-0049/05 A I L B 20060101 20051128 H EP
NOTE:
Figure number on first page: 4b
LANGUAGE (Publication,Procedural,Application): English; English; English
FULLTEXT AVAILABILITY:
Available Text Language Update Word Count
CLAIMS A (English) 200607 796
SPEC A (English) 200607 4595
Total word count - document A 5391
Total word count - document B 0
Total word count - documents A + B 5391

INTERNATIONAL CLASSIFICATION (V8 + ATTRIBUTES):
IPC + Level Value Position Status Version Action Source Office:
G11B-0005/31 A I F B 20060101 20051128 H EP...

... **G11B-0005/39** A I L B 20060101 20051128 H EP

...SPECIFICATION of a cluster of MR devices. The ELGs are monitored during manufacturing to determine the **stripe height** of the **active MR** devices of the cluster. For example, the lapping process is controlled to cease when the...

13/3,K/2 (Item 2 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS
(c) 2006 European Patent Office. All rts. reserv.

01675190
Flux guide in the bearing surface of a magnetoresistive head

Flussleiter in der Laufflache eines Magnetowiderstandkopfes
Guide de flux dans la surface portante d'une tete magnetoresistive
PATENT ASSIGNEE:
QUANTUM CORPORATION, (567673), 501 Sycamore Drive, Milpitas, CA 95035, (US), (Applicant designated States: all)
INVENTOR:
Wu, Andrew L., 15 High Street, Shrewsbury, Massachussets 01545, (US)
LEGAL REPRESENTATIVE:
Charig, Raymond Julian et al (79692), Eric Potter Clarkson, Park View House, 58 The Ropewalk, Nottingham NG1 5DD, (GB)
PATENT (CC, No, Kind, Date): EP 1376543 A2 040102 (Basic)
EP 1376543 A3 050817
APPLICATION (CC, No, Date): EP 2003253992 030625;
PRIORITY (CC, No, Date): US 183329 020625
DESIGNATED STATES: AT; BE; BG; CH; CY; CZ; DE; DK; EE; ES; FI; FR; GB; GR; HU; IE; IT; LI; LU; MC; NL; PT; RO; SE; SI; SK; TR
EXTENDED DESIGNATED STATES: AL; LT; LV; MK
INTERNATIONAL PATENT CLASS (V7): **G11B-005/39** ; **G11B-005/31** ; H01L-043/00; H01F-010/32
ABSTRACT WORD COUNT: 39
NOTE:
Figure number on first page: 2

LANGUAGE (Publication,Procedural,Application): English; English; English
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS A	(English)	200401	307
SPEC A	(English)	200401	3365
Total word count - document A			3672
Total word count - document B			0
Total word count - documents A + B			3672

INTERNATIONAL PATENT CLASS (V7): **G11B-005/39** ...

... **G11B-005/31**

...SPECIFICATION CoFe and the AFM exhange materials, being exposed on the TBS. It also allows the **GMR** element stripe height to be defined by high precision photolithographic techniques as opposed to the less controllable mechanical...
...surface of the GMR film is not etched but instead lapped to achieve a desired **GMR element stripe height** . It is critical to accurately control the size of the GMR element during the lapping...

...materials typically encountered on the tape bearing surface in contact with the magnetic tape. The **GMR element stripe height** , indicated by the reference numeral 180, is the NiFe height defined by the back side ...

13/3,K/3 (Item 3 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

01652100
Variable width flat magnetic-tape head for bi-directional contact recording and method for making the same
Flachmagnetbandkopf mit variabler Breite fur bi-direktionale Aufnahme und Verfahren dieses herzustellen
Tete plane pour bande magnetique a largeur variable pour enregistrement

bi-directionel et methode de fabrication pour celle ci

PATENT ASSIGNEE:
QUANTUM CORPORATION, (567673), 501 Sycamore Drive, Milpitas, CA 95035, (US), (Applicant designated States: all)
INVENTOR:
Kaiser, Donna Jean, 13 Angel Road, North Reading, Massachusetts 01864-2902, (US)
Kennedy, James, 226 Boston Road, Palmer, Massachusetts 01069, (US)
LEGAL REPRESENTATIVE:
Charig, Raymond Julian et al (79692), Eric Potter Clarkson, Park View House, 58 The Ropewalk, Nottingham NG1 5DD, (GB)
PATENT (CC, No, Kind, Date): EP 1359577 A2 031105 (Basic)
APPLICATION (CC, No, Date): EP 2003252370 030414;
PRIORITY (CC, No, Date): US 128100 020423
DESIGNATED STATES: AT; BE; BG; CH; CY; CZ; DE; DK; EE; ES; FI; FR; GB; GR; HU; IE; IT; LI; LU; MC; NL; PT; RO; SE; SI; SK; TR
EXTENDED DESIGNATED STATES: AL; LT; LV; MK
INTERNATIONAL PATENT CLASS (V7): **G11B-015/62**
ABSTRACT WORD COUNT: 184
NOTE:
Figure number on first page: 1

LANGUAGE (Publication,Procedural,Application): English; English; English
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS A	(English)	200345	383
SPEC A	(English)	200345	5483
Total word count - document A			5866
Total word count - document B			0
Total word count - documents A + B			5866

INTERNATIONAL PATENT CLASS (V7): **G11B-015/62**

...ABSTRACT simpler and less costly to manufacture than comparable devices with distinct advantages to the magnetoresistive (" **MR** ") read **element stripe height** control process, device alignment and assembly processes particularly with respect to traditionally contoured tape heads...

...SPECIFICATION its simplicity of fabrication and the elimination of many traditionally used processing operations. The magnetoresistive (" **MR** ") read **element stripe height** may be controlled with a single operation (flat lapping) rather than the multiple steps required...

...is simpler and less costly to manufacture than comparable devices with distinct advantages to the **MR** read **element stripe height** control process, device alignment and assembly processes, particularly with respect to traditionally contoured tape heads...

13/3,K/4 (Item 4 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

01017403
Method and system for making magnetic recording servo tracks with inherent dropout robustness and with encoded track set information, longitudinal position info
Methode und System zur Herstellung von Magnetaufzeichnungservospuren mit inharenter Robustheit gegen Ausfalle und mit wahrend der Band- oder Plattenherstellung

Methode et systeme pour faire des pistes d'asservissement a enregistrement magnetique avec resistance inherente a la perte de signal et avec de l'information en

PATENT ASSIGNEE:
Tandberg Data ASA, (465945), Kjelsasveien 161, 0884 Oslo, (NO),
(applicant designated states:
AT;BE;CH;CY;DE;DK;ES;FI;FR;GB;GR;IE;IT;LI;LU;MC;NL;PT;SE)
INVENTOR:
Pahr, Per Olaf, Fjellstien 3B, 3400 Lier, (NO)
LEGAL REPRESENTATIVE:
Tonhardt, Marion, Dr. et al (69411), Forrester & Boehmert,
Franz-Joseph-Strasse 38, 80801 Munchen, (DE)
PATENT (CC, No, Kind, Date): EP 911813 A1 990428 (Basic)
APPLICATION (CC, No, Date): EP 98109848 980529;
PRIORITY (CC, No, Date): US 956115 971024
DESIGNATED STATES: DE
INTERNATIONAL PATENT CLASS (V7): **G11B-005/584** ; **G11B-005/55** ; **G11B-015/087** ; **G11B-023/36** ; **G11B-027/28**
ABSTRACT WORD COUNT: 101

LANGUAGE (Publication,Procedural,Application): English; English; English
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS A	(English)	9917	651
SPEC A	(English)	9917	4960
Total word count - document A			5611
Total word count - document B			0
Total word count - documents A + B			5611

INTERNATIONAL PATENT CLASS (V7): **G11B-005/584** ...

... **G11B-005/55** ...

... **G11B-015/087** ...

... **G11B-023/36** ...
... **G11B-027/28**

...SPECIFICATION shown, for example, in Figure 3 of Robert E. Fontana et al. "Submicron Trackwidth and **Stripe Height MR Sensor** Test Structures" (IEEE Transactions on Magnetics, Vol. 32, No. 5, Sept. 1996, pp. 3340-3442...

13/3,K/5 (Item 5 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

00873897
Giant magnetoresistive transducer with increased output signal
Riesenmagnetoresistive Wandler mit erhohtem Ausgangssignal
Transducteurs a effet magnetoresistif geant avec un signal de sortie augmente
PATENT ASSIGNEE:
READ-RITE CORPORATION, (824840), 345 Los Coches Street, Milpitas
California 95035, (US), (applicant designated states: DE;NL)
INVENTOR:
Yuan, Samuel W., 160, Oaks View Drive, San Carlos, California 94070, (US)
LEGAL REPRESENTATIVE:
Korber, Wolfhart, Dr. rer.nat. et al (44475), Patentanwalte Mitscherlich

& Partner, Sonnenstrasse 33, 80331 Munchen, (DE)
PATENT (CC, No, Kind, Date): EP 801380 A2 971015 (Basic)
EP 801380 A3 980304
APPLICATION (CC, No, Date): EP 97104983 970324;
PRIORITY (CC, No, Date): US 629993 960410
DESIGNATED STATES: DE; NL
INTERNATIONAL PATENT CLASS (V7): **G11B-005/39**
ABSTRACT WORD COUNT: 86
LANGUAGE (Publication,Procedural,Application): English; English; English
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS A	(English)	9710W2	197
SPEC A	(English)	9710W2	1865
Total word count - document A			2062
Total word count - document B			0
Total word count - documents A + B			2062

INTERNATIONAL PATENT CLASS (V7): **G11B-005/39**

...SPECIFICATION when the sensor height is comparable to the transmission line decay length.
In the CPP/ **GMR** mode, the " **active** " **GMR stripe height** is defined by the contact leads. Therefore, the following situation results when the sensor height...

13/3,K/6 (Item 6 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

00839468
Longitudinally biased magnetoresistive sensor having a concave shaped active region to reduce Barkhausen noise by achieving a substantially single magnetic doma
Longitudinal vorgespannter magnetoresistiver Sensor mit konkav geformtem Aktivgebiet zur Reduzierung von Barkhausen-Gerausch durch Erreichen eines im wesentlich
Detecteur magnetoresistif polarise longitudinalement comportant une region active de forme concave pour reduire le bruit de Barkhausen en etablissant un etat ma
PATENT ASSIGNEE:
QUANTUM CORPORATION, (567671), 500 McCarthy Boulevard, Milpitas California 95035, (US), (applicant designated states: DE;FR;GB;IT;NL)
INVENTOR:
Mallary, Michael L., 113 Boylston Rd., Berlin, Massachusetts 01503, (US)
LEGAL REPRESENTATIVE:
Goodman, Christopher (31122), Eric Potter Clarkson, Park View House, 58 The Ropewalk, Nottingham NG1 5DD, (GB)
PATENT (CC, No, Kind, Date): EP 777214 A2 970604 (Basic)
EP 777214 A3 981111
APPLICATION (CC, No, Date): EP 96308390 961120;
PRIORITY (CC, No, Date): US 565032 951130
DESIGNATED STATES: DE; FR; GB; IT; NL
INTERNATIONAL PATENT CLASS (V7): **G11B-005/39** ; **G11B-005/012**
LANGUAGE (Publication,Procedural,Application): English; English; English
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS A	(English)	EPAB97	1590
SPEC A	(English)	EPAB97	6632
Total word count - document A			8222

Total word count - document B 0
Total word count - documents A + B 8222

INTERNATIONAL PATENT CLASS (V7): **G11B-005/39** ...

... **G11B-005/012**

...SPECIFICATION In a preferred embodiment, a substantially constant effective longitudinal bias field is obtained throughout the **active MR element** if the **stripe height** increases as an exponential function of the square of the off-track distance.
In a...distance ARMAX)) along the central longitudinal axis and ABMIN)) at the edge portions of the **MR sensor** 80. The **stripe height** of the active region is substantially SH2)) over the length ARMIN)) and lesser out toward...

13/3,K/7 (Item 7 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

00724907
Giant magnetoresistive reproduce head.
Riesenmagnetoresistiven Wiedergabekopf.
Tete de reproduction a magnetoresistance geant.
PATENT ASSIGNEE:
EASTMAN KODAK COMPANY, (201214), 343 State Street, Rochester, New York 14650-2201, (US), (applicant designated states: DE;FR;GB)
INVENTOR:
Smith, Neil, c/o Eastman Kodak Co., Patent Legal Staff, 343 State Street, Rochester, New York 14650-2201, (US)
LEGAL REPRESENTATIVE:
Weber, Etienne Nicolas et al (91684), Kodak Industrie, Departement Brevets, CRT, Zone Industrielle, 71102 Chalon sur Saone Cedex, (FR)
PATENT (CC, No, Kind, Date): EP 684484 A2 951129 (Basic)
EP 684484 A3 960110
APPLICATION (CC, No, Date): EP 95420129 950512;
PRIORITY (CC, No, Date): US 248772 940525
DESIGNATED STATES: DE; FR; GB
INTERNATIONAL PATENT CLASS (V7): G01R-033/09; **G11B-005/39**
ABSTRACT WORD COUNT: 166
LANGUAGE (Publication,Procedural,Application): English; English; English
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS A	(English)	EPAB95	930
SPEC A	(English)	EPAB95	6087
Total word count - document A			7017
Total word count - document B			0
Total word count - documents A + B			7017

...INTERNATIONAL PATENT CLASS (V7): **G11B-005/39**

...SPECIFICATION that of the interior magnetic layer 20 thickness t. For high density reproduce heads, the **stripe height** L of the **GMR** -DMR **sensor** structure 10 is about 1 micron.
Magnetic layers 16, 18, 20, are generally deposited in...

13/3,K/8 (Item 8 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

00690133

Individual MR transducer head/disk/channel adaptive bias current system

Adaptives Vormagnetisierungssystem fur Individual- MR-Wandlerkopf/-Platte/-Kanal

Systeme a courant de premagnetisation adaptatif pour transducteurs MR tete/disque/canal individuels

PATENT ASSIGNEE:
International Business Machines Corporation, (200120), Old Orchard Road, Armonk, N.Y. 10504, (US), (Proprietor designated states: all)
INVENTOR:
Christner, Jodie Ann, 1135 Chippewa Drive N.W., Rochester, Minnesota 55901, (US)
Cunningham, Earl A., 2429 13th Avenue N.W., Rochester, Minnesota 55901, (US)
Kerwin, Gregory John, 6405 50th Avenue N.W., Rochester, Minnesota 55901, (US)
Poss, Joe Martin, 4901 Countrywood Drive S.E., Rochester, Minnesota 55904, (US)
LEGAL REPRESENTATIVE:
de Pena, Alain (15151), Compagnie IBM France Departement de Propriete Intellectuelle, 06610 La Gaude, (FR)

PATENT (CC, No, Kind, Date): EP 658879 A2 950621 (Basic)
EP 658879 A3 951102
EP 658879 B1 011031
APPLICATION (CC, No, Date): EP 94480137 941115;
PRIORITY (CC, No, Date): US 168630 931216
DESIGNATED STATES: DE; FR; GB
INTERNATIONAL PATENT CLASS (V7): **G11B-005/035** ; **G11B-005/02** ; **G11B-005/012** ; **G11B-019/02**
ABSTRACT WORD COUNT: 152
NOTE:
Figure number on first page: 3

LANGUAGE (Publication,Procedural,Application): English; English; English
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS A	(English)	EPAB95	836
CLAIMS B	(English)	200144	745
CLAIMS B	(German)	200144	662
CLAIMS B	(French)	200144	902
SPEC A	(English)	EPAB95	4191
SPEC B	(English)	200144	4224
Total word count - document A			5028
Total word count - document B			6533
Total word count - documents A + B			11561

INTERNATIONAL PATENT CLASS (V7): **G11B-005/035** ...

... **G11B-005/02** ...

... **G11B-005/012** ...

... **G11B-019/02**

...SPECIFICATION temperature and current density compound and cause a much shorter life expectancy for the low **stripe height** and thin **MR elements** , compared to the higher and thicker elements.
Another consideration is that all the factors that...

...SPECIFICATION temperature and current density compound and cause a much shorter life expectancy for the low **stripe height** and thin **MR elements** , compared to the higher and thicker elements.
Another consideration is that all the factors that...

13/3,K/9 (Item 9 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

00599450
Amplifier for magnetoresistive sensor
Verstarker fur einen magnetoresistiven Sensor
Amplificateur pour un capteur magnetoresistif
PATENT ASSIGNEE:
International Business Machines Corporation, (200120), Old Orchard Road, Armonk, N.Y. 10504, (US), (applicant designated states: DE;FR;GB)
INVENTOR:
Jove, Stephen Alan, P O Box 456, Watsonville, 95077-0456, (US)
Klaassen, Klaas Berend, 7171 Anjou Creek Circle, San Jose, California 95120, (US)
van Peppen, Jacobus Cornelis Leonardus, 841 Portswood Circle, San Jose, California 95120, (US)
LEGAL REPRESENTATIVE:
Burt, Roger James, Dr. (52152), IBM United Kingdom Limited Intellectual Property Department Hursley Park, Winchester Hampshire SO21 2JN, (GB)
PATENT (CC, No, Kind, Date): EP 586062 A1 940309 (Basic)
EP 586062 B1 980225
APPLICATION (CC, No, Date): EP 93305533 930714;
PRIORITY (CC, No, Date): US 914278 920715
DESIGNATED STATES: DE; FR; GB
INTERNATIONAL PATENT CLASS (V7): **G11B-005/02** ; **G11B-020/24** ; G01R-033/06
ABSTRACT WORD COUNT: 125

LANGUAGE (Publication,Procedural,Application): English; English; English
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS B	(English)	9809	698
CLAIMS B	(German)	9809	678
CLAIMS B	(French)	9809	779
SPEC B	(English)	9809	3147
Total word count - document A			0
Total word count - document B			5302
Total word count - documents A + B			5302

INTERNATIONAL PATENT CLASS (V7): **G11B-005/02** ...

... **G11B-020/24**

...SPECIFICATION Patent 4,706,138, to render the amplifier output signal relatively insensitive to variations in **stripe height** of the **MR sensors** ; and
(8) Use, with a single-ended amplifier, of a disk enclosure as a Faraday...conductive substrate of disk D are grounded to minimize transient conductive asperity currents between a **striped portion** (not shown) of **MR element** Rmr and an air bearing surface of the associated disk D with protruding conductive asperities...Vout of the amplifier circuit relatively insensitive to variations in signal due to variations in **stripe height** of the **MR element** .

It will be apparent to one skilled in the art that notwithstanding embodiments of the...

...CLAIMS and the conductive substrate are grounded to substantially minimise transient conductive asperity current between a **striped portion** of the **MR element** and the recording surface.
8. A magnetic storage system as claimed in claim 7 further...

13/3,K/10 (Item 10 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

00536660
Process for controlling the manufacture of magnetic recording heads using lapping guides.
Verfahren zur Steuerung des Lappens von Aufzeichnungsmagnetkopfen mittels Lappungsfuhrung.
Procede de commande de fabrication de tetes magnetiques d'enregistrement utilisant des guides de rodage.
PATENT ASSIGNEE:
International Business Machines Corporation, (200120), Old Orchard Road, Armonk, N.Y. 10504, (US), (applicant designated states: DE;FR;GB)
INVENTOR:
Zammit, Robert Paul, 4558 North Rockcliff Road, Tucson,Arizona 85715, (US)
LEGAL REPRESENTATIVE:
Burt, Roger James, Dr. (52152), IBM United Kingdom Limited Intellectual Property Department Hursley Park, Winchester Hampshire SO21 2JN, (GB)
PATENT (CC, No, Kind, Date): EP 500230 A2 920826 (Basic)
EP 500230 A3 930113
APPLICATION (CC, No, Date): EP 92300920 920204;
PRIORITY (CC, No, Date): US 656666 910219
DESIGNATED STATES: DE; FR; GB
INTERNATIONAL PATENT CLASS (V7): **G11B-005/31** ; **G11B-005/39**
ABSTRACT WORD COUNT: 173

LANGUAGE (Publication,Procedural,Application): English; English; English
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS A	(English)	EPABF1	585
SPEC A	(English)	EPABF1	5194
Total word count - document A			5779
Total word count - document B			0
Total word count - documents A + B			5779

INTERNATIONAL PATENT CLASS (V7): **G11B-005/31** ...

... **G11B-005/39**

...SPECIFICATION the invention. For instance, the present invention is preferable for use in determining the required **stripe height** of **MR** read **elements** in magnetic heads for use with tape media. It should be understood that other uses...

13/3,K/11 (Item 11 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

00206445
A magnetoresistive read transducer assembly.
Zusammensetzung eines magnetoresistiven Lesewandlers.
Assemblage de transducteur de lecture magnetoresistif.
PATENT ASSIGNEE:
International Business Machines Corporation, (200120), Old Orchard Road, Armonk, N.Y. 10504, (US), (applicant designated states: DE;FR;GB)
INVENTOR:
Huang, Shiezen, 6946 Randol Creek Drive, San Jose, Cal. 95120, (US)
Voegeli, Otto, 13465 Sycamore Avenue, Morgan Hill, Cal. 95037, (US)
LEGAL REPRESENTATIVE:
Hobbs, Francis John (31881), IBM United Kingdom Limited Intellectual Property Department Hursley Park, Winchester Hampshire SO21 2JN, (GB)
PATENT (CC, No, Kind, Date): EP 211445 A1 870225 (Basic)
EP 211445 B1 900725
APPLICATION (CC, No, Date): EP 86110983 860808;
PRIORITY (CC, No, Date): US 765999 850815
DESIGNATED STATES: DE; FR; GB
INTERNATIONAL PATENT CLASS (V7): **G11B-005/39**
ABSTRACT WORD COUNT: 72
LANGUAGE (Publication,Procedural,Application): English; English; English
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS B	(English)	EPABF1	242
SPEC B	(English)	EPABF1	2642
Total word count - document A			0
Total word count - document B			2884
Total word count - documents A + B			2884

INTERNATIONAL PATENT CLASS (V7): **G11B-005/39**

...SPECIFICATION Figure 6 and having the following dimensions, and this sensor had suitable performance characteristics. The **sensor** has an **MR stripe height** of 10 (mu)m, and comb extensions that are 50 (mu)m long, and 2...

13/3,K/12 (Item 12 from file: 348)
DIALOG(R)File 348:EUROPEAN PATENTS

00206271
Method and apparatus for reading recorded data by a magnetoresistive head.
Verfahren und Gerat zum Ablesen aufgezeichneter Daten mit einem magnetoresistiven Kopf.
Procede et appareil de lecture au moyen d'une tete magnetoresistive de donnees enregistrees.
PATENT ASSIGNEE:
International Business Machines Corporation, (200120), Old Orchard Road, Armonk, N.Y. 10504, (US), (applicant designated states: DE;FR;GB;IT)
INVENTOR:
Klaassen, Klaas Berend, 7171 Anjou Circle, San Jose CA 95120, (US)
LEGAL REPRESENTATIVE:
Burt, Roger James, Dr. (52152), IBM United Kingdom Limited Intellectual Property Department Hursley Park, Winchester Hampshire SO21 2JN, (GB)
PATENT (CC, No, Kind, Date): EP 215270 A1 870325 (Basic)
EP 215270 B1 921230
APPLICATION (CC, No, Date): EP 86110796 860805;
PRIORITY (CC, No, Date): US 767549 850820
DESIGNATED STATES: DE; FR; GB; IT

INTERNATIONAL PATENT CLASS (V7): **G11B-005/39**
ABSTRACT WORD COUNT: 70

LANGUAGE (Publication,Procedural,Application): English; English; English
FULLTEXT AVAILABILITY:

Available Text	Language	Update	Word Count
CLAIMS B	(English)	EPBBF1	965
CLAIMS B	(German)	EPBBF1	971
CLAIMS B	(French)	EPBBF1	1095
SPEC B	(English)	EPBBF1	2940
Total word count - document A			0
Total word count - document B			5971
Total word count - documents A + B			5971

INTERNATIONAL PATENT CLASS (V7): **G11B-005/39**

...SPECIFICATION recording applications. Since both R(sub(h)) and, more importantly, R(sub(h)) are proportional **to stripe height** prior art preamplifiers which detect V(sub(s)) of equation (A) provide different sensistivity if...

13/3,K/13 (Item 1 from file: 349)
DIALOG(R)File 349:PCT FULLTEXT

00873008 **Image available**
PROCESS AND APPARATUS FOR FINISHING A MAGNETIC SLIDER
PROCEDE ET APPAREIL DE FINITION D'UN PLAN PORTEUR DE TETE MAGNETIQUE
Patent Applicant/Assignee:
SEAGATE TECHNOLOGY LLC, 920 Disc Drive, Scotts Valley, CA 95066, US, US (Residence), US (Nationality)
Inventor(s):
BOUTAGHOU Zine-Eddine, 307 Lily Pond Lane, Vadnais Heights, MN 55127, US,

Legal Representative:
BOHN David C (et al) (agent), Westman, Champlin & Kelly, P.A., Suite 1600 - International Centre, 900 Second Avenue South, Minneapolis, MN 55402-3319, US,
Patent and Priority Information (Country, Number, Date):
Patent: WO 200207154 A2-A3 20020124 (WO 0207154)
Application: WO 2001US21561 20010709 (PCT/WO US0121561)
Priority Application: US 2000218262 20000713
Designated States:
(Protection type is "patent" unless otherwise stated - for applications prior to 2004)
AE AG AL AM AT AU AZ BA BB BG BR BY BZ CA CH CN CR CU CZ DE DK DM DZ EE ES FI GB GD GE GH GM HR HU ID IL IN IS JP KE KG KP KR KZ LC LK LR LS LT LU LV MA MD MG MK MN MW MX MZ NO NZ PL PT RO RU SD SE SG SI SK SL TJ TM TR TT TZ UA UG UZ VN YU ZA ZW
(EP) AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE TR
(OA) BF BJ CF CG CI CM GA GN GW ML MR NE SN TD TG
(AP) GH GM KE LS MW MZ SD SL SZ TZ UG ZW
(EA) AM AZ BY KG KZ MD RU TJ TM
Publication Language: English
Filing Language: English
Fulltext Word Count: 3121

Main International Patent Class (v7): **G11B-005/10**
International Patent Class (v7): **G11B-005/187** ...

... **G11B-005/31** ...

... **G11B-005/39**
Fulltext Availability:
Detailed Description

Detailed Description
... row of multiple read/write heads. The bars are then lapped to adjust an average **stripe height** (SH) of magnetoresistive (**MR**) **transducers** in the bar, the average throat height (TH) of inductive transducer in the bar, or...

13/3,K/14 (Item 2 from file: 349)
DIALOG(R)File 349:PCT FULLTEXT

00734850 **Image available**
METHOD FOR CONTROLLING BIAS CURRENT FOR MAGNETORESISTIVE HEAD, FIXED MAGNETIC RECORDING DEVICE, AND MAGNETIC DISC THEREFOR
PROCEDE DE COMMANDE DU COURANT DE POLARISATION POUR TETE A MAGNETORESISTANCE, DISPOSITIF D'ENREGISTREMENT MAGNETIQUE FIXE ET DISQUE MAGNETIQUE AFFERENT
Patent Applicant/Assignee:
MATSUSHITA ELECTRIC INDUSTRIAL CO LTD, 1006, Oaza Kadoma, Kadoma-shi, Osaka 571-8501, JP, JP (Residence), JP (Nationality), (For all designated states except: US)
Patent Applicant/Inventor:
KADOKAWA Kouichi, 2-7-133, Shinonomecho, Niihama-shi, Ehime 792-0864, JP, JP (Residence), JP (Nationality), (Designated only for: US)
Legal Representative:
MORIMOTO Yoshihiro, All Nippon Airways(Nishi-Hommachi)bldg., 4th Floor, 10-10, Nishi-Hommachi 1-chome, Nishi-ku, Osaka-shi, Osaka 550-0005, JP
Patent and Priority Information (Country, Number, Date):
Patent: WO 200048173 A1 20000817 (WO 0048173)
Application: WO 2000JP770 20000214 (PCT/WO JP0000770)
Priority Application: JP 9935100 19990215
Designated States:
(Protection type is "patent" unless otherwise stated - for applications prior to 2004)
CN ID KR SG US
Publication Language: English
Filing Language: English
Fulltext Word Count: 11642

Main International Patent Class (v7): **G11B-005/02**
International Patent Class (v7): **G11B-005/012** ...

... **G11B-019/02** ...

... **G11B-019/04**
Fulltext Availability:
Detailed Description

Detailed Description
... Thus, temperature and current density compound and cause a much shorter life expectancy for low- **stripe - height** and thin **MR elements** , compared to higher and thicker elements.

Another consideration is that all the factors that make...

13/3,K/15 (Item 3 from file: 349)
DIALOG(R)File 349:PCT FULLTEXT

00541177 **Image available**
METHOD AND APPARATUS FOR BIASING A MAGNETORESISTIVE HEAD WITH CONSTANT POWER DISSIPATION
PROCEDE ET APPAREIL UTILES POUR POLARISER UNE TETE MAGNETORESISTANTE AVEC UNE DISSIPATION DE PUISSANCE CONSTANTE
Patent Applicant/Assignee:
SEAGATE TECHNOLOGY INC, 920 Disc Drive, Scotts Valley, CA 95066, US, US (Residence), US (Nationality)
Inventor(s):
IONESCU Stefan A, 19405 Oak Ridge Court West, Burnsville, MN 55306, US,
RUB Bernardo, 6608 Scandia Road, Edina, MN 55439, US,
Legal Representative:
WIBERG John A (agent), Westman, Champlin & Kelly, P.A., Suite 1600 - International Centre, 900 Second Avenue South, Minneapolis, MN 55402-3319 (et al), US,
Patent and Priority Information (Country, Number, Date):
Patent: WO 200004550 A2-A3 20000127 (WO 0004550)
Application: WO 99US16210 19990715 (PCT/WO US9916210)
Priority Application: US 9893101 19980716
Designated States:
(Protection type is "patent" unless otherwise stated - for applications prior to 2004)
CN DE GB JP KR SG
Publication Language: English
Filing Language: English
Fulltext Word Count: 4571

Main International Patent Class (v7): **G11B-005/02**
International Patent Class (v7): **G11B-005/012**
Fulltext Availability:
Detailed Description

Detailed Description
... MR head with a relatively short stripe height will have a higher resistance than an **MR head** having a taller **stripe height** and will therefor dissipate more power. The **MR head** having the shorter **stripe height** will therefor operate at a higher temperature than the **MR head** having the taller **stripe height** . Product life is inversely related to operating temperature. Thus the life expectancy for the low **stripe height** and thin **MR elements** is much shorter than for the higher and thicker MR elements. Thus, in a disc...

13/3,K/16 (Item 4 from file: 349)
DIALOG(R)File 349:PCT FULLTEXT

00238255
MAGNETORESISTIVE HEAD WITH INTEGRATED BIAS AND MAGNETIC SHIELD LAYER
TETE DE LECTURE A RESISTANCE MAGNETIQUE, A COUCHE DE BLINDAGE MAGNETIQUE ET

DE POLARISATION INCORPORES

Patent Applicant/Assignee:
MINNESOTA MINING AND MANUFACTURING COMPANY,
Inventor(s):
SCHWARZ Theodore A,
BISCHOFF Peter G,
LEUNG Chak M,
CHEN Johnny C,
THAYAMBALLI Pradeep,

Patent and Priority Information (Country, Number, Date):
Patent: WO 9312519 A1 19930624
Application: WO 92US10645 19921210 (PCT/WO US9210645)
Priority Application: US 91809678 19911218
Designated States:
(Protection type is "patent" unless otherwise stated - for applications prior to 2004)
JP KR AT BE CH DE DK ES FR GB GR IE IT LU MC NL PT SE
Publication Language: English
Fulltext Word Count: 4973

Main International Patent Class (v7): **G11B-005/39**
Fulltext Availability:
Detailed Description

Detailed Description

... away from that plane, which is in the range of one to ten times the **stripe height** of the **MR element** , thereby concentrating both the current passing through said electrically-conductive, magnetically-permeable layer and the...